

Curso de Verão

Departamento de Física – UFPE

2024

Recife-PE

22 de Janeiro a **09 de Fevereiro**



Minicurso 3:

Materiais Bidimensionais

Prof. Lídia C. Gomes

Dia 1 (29/01)

General introduction.

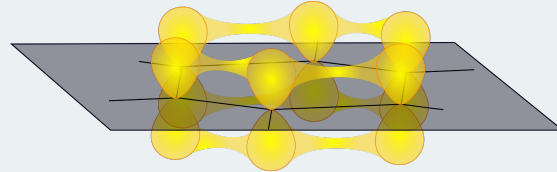
What are 2D materials?

A tiny bit of history.

Some interesting properties.

Dia 2 (30/01)

The origin of dimensionality: an analysis of orbital hybridization in graphene.



Dia 3 (31/01)

Synthesis methods.

Some experimental achievements.

Some help from computers: ML discovery and development of new 2D materials.

2004-2007

Licenciatura em Física - PUC MG

2008-2010

Mestrado em Física - UFMG

2010-2014

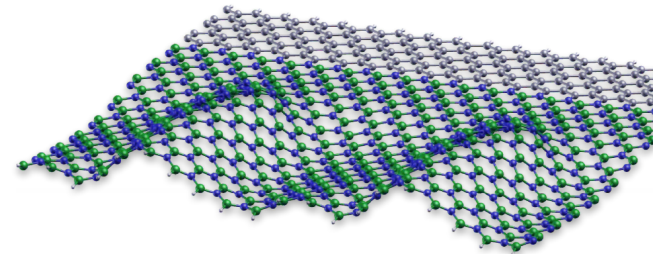
Doutorado em Física - UFMG

2014-2017

Pós-Doutorado - CA2DM, NUS



Centre for
Advanced 2D Materials



2017-2019

Pós-Doutorado - NCSA, UIUC

2020-2021

Pós-Doutorado - UIUC + IFT, UNESP

2022

Profa Adjunta - UFPE

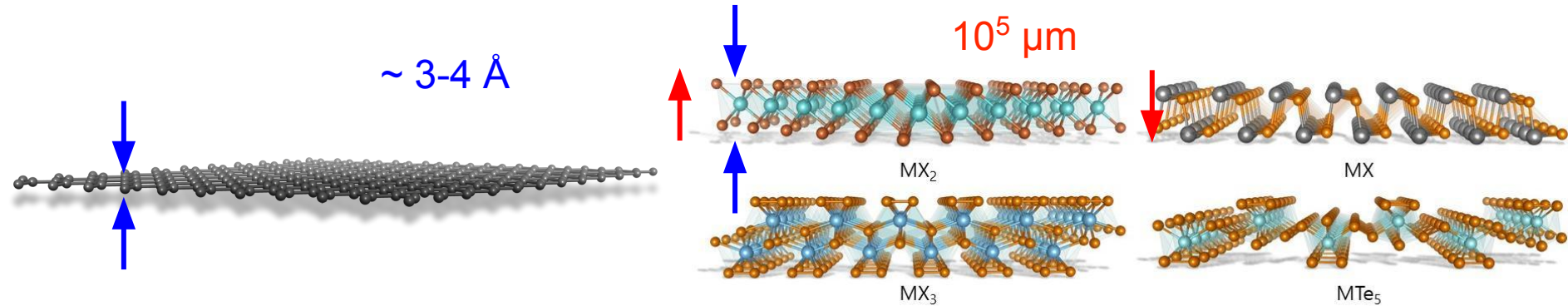


Materials ~~bidimensionais~~ atomicamente finos

O que são?

Cristais com um ou poucos átomos de espessura

Interações eletrônicas no plano são muito mais fortes do que aquelas na direção perpendicular ao plano.

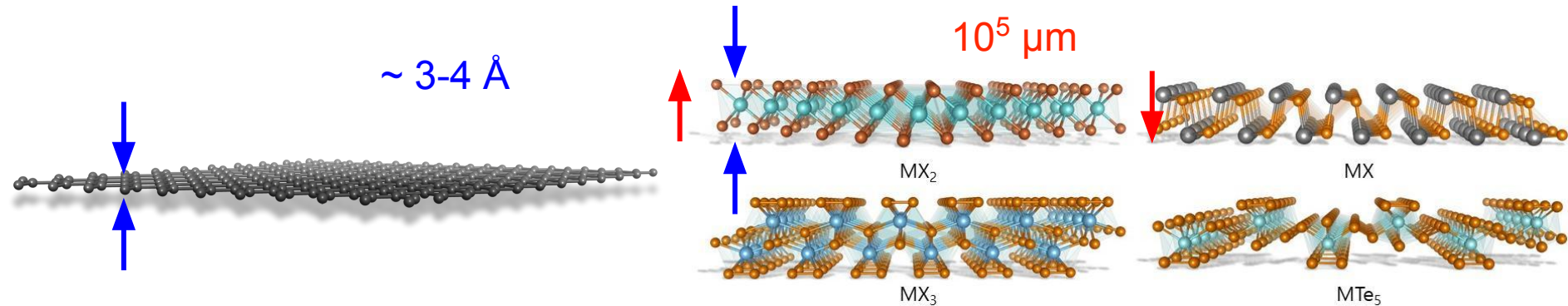


Materiais ~~bidimensionais~~ atômicamente finos

O que são?

Cristais com um ou poucos átomos de espessura

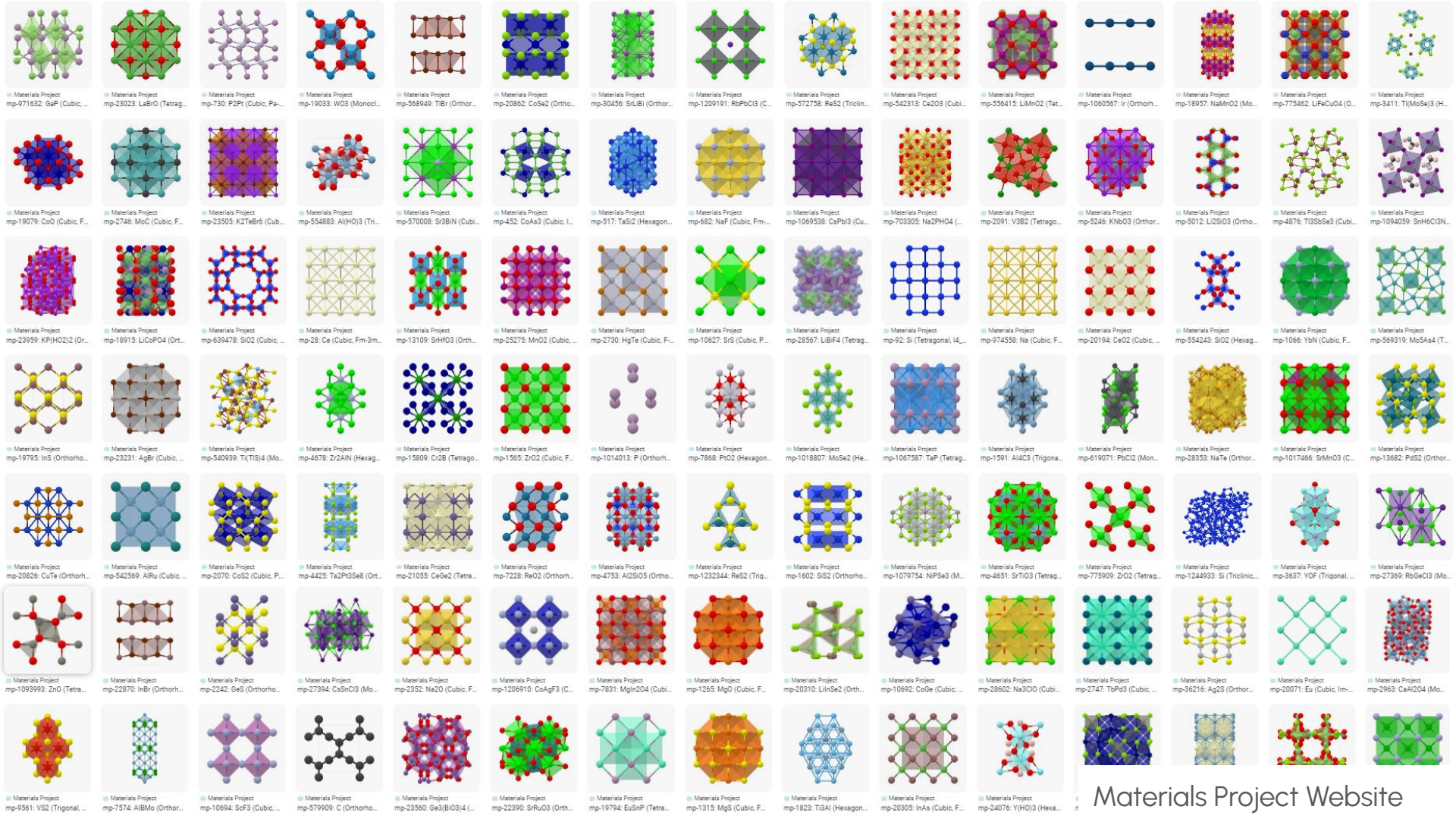
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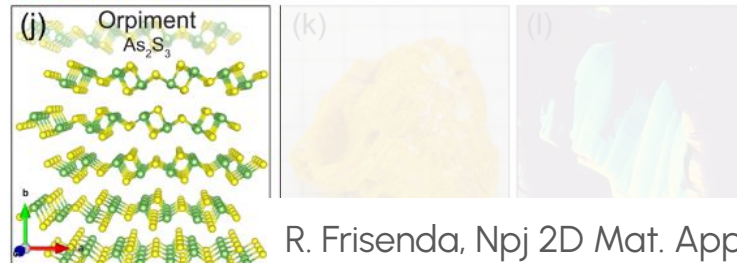
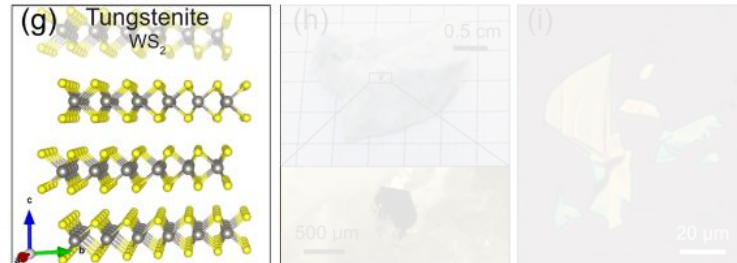
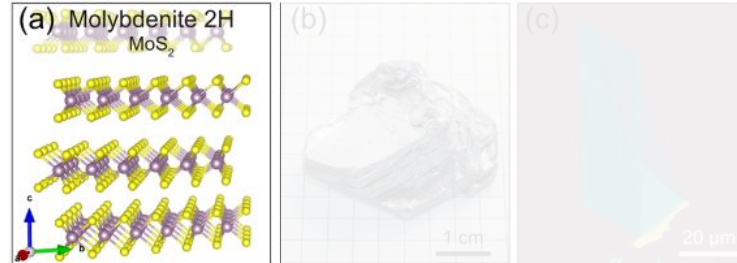
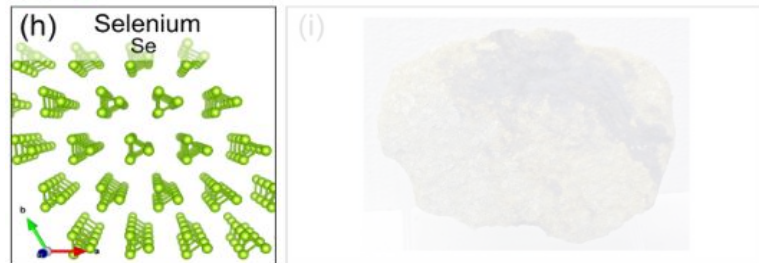
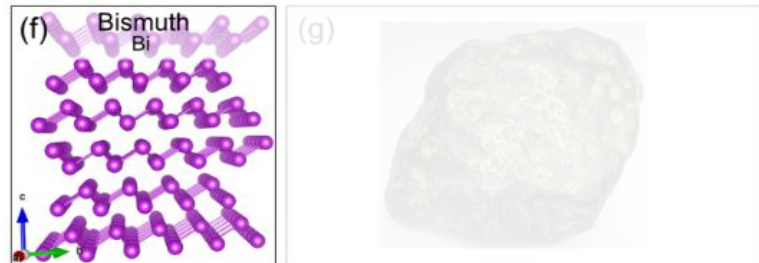
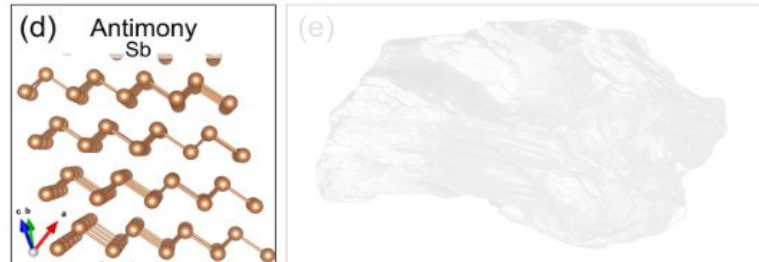


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	1	<table border="1"> <tr> <td rowspan="3">1 H Hydrogen 1.008</td> <td colspan="2">Atomic Symbol Name Weight</td> <td rowspan="3"> C Solid Hg Liquid H Gas Rf Unknown </td> <td colspan="6">Metals</td> <td rowspan="3">Metalloids</td> <td colspan="3">Nonmetals</td> <td rowspan="3"> 2 He Helium 4.0026 </td> </tr> <tr> <td>3</td> <td>4</td> <td rowspan="2">Alkali metals</td> <td rowspan="2">Alkaline earth metals</td> <td>Lanthanoids</td> <td rowspan="2">Transition metals</td> <td rowspan="2">Post-transition metals</td> <td rowspan="2">Reactive nonmetals</td> <td rowspan="2">Noble gases</td> </tr> <tr> <td>11</td> <td>12</td> <td>Actinoids</td> </tr> </table>														1 H Hydrogen 1.008	Atomic Symbol Name Weight		C Solid Hg Liquid H Gas Rf Unknown	Metals						Metalloids	Nonmetals			2 He Helium 4.0026	3	4	Alkali metals	Alkaline earth metals	Lanthanoids	Transition metals	Post-transition metals	Reactive nonmetals	Noble gases	11	12	Actinoids	5	6	7	8	9	10	11	12	13	14	15	16	17	18
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6	55	56	57-71	72	73	74	75	76	77	78	79	80	81	82	83	84	85	86	87	88	89-103	104	105	106	107	108	109	110	111	112	113	114	115	116	117	118																				
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	87	88	89-103	104	105	106	107	108	109	110	111	112	113	114	115	116	117	118	119	120	121	122	123	124	125	126	127	128	129	130	131	132	133	134	135	136																				

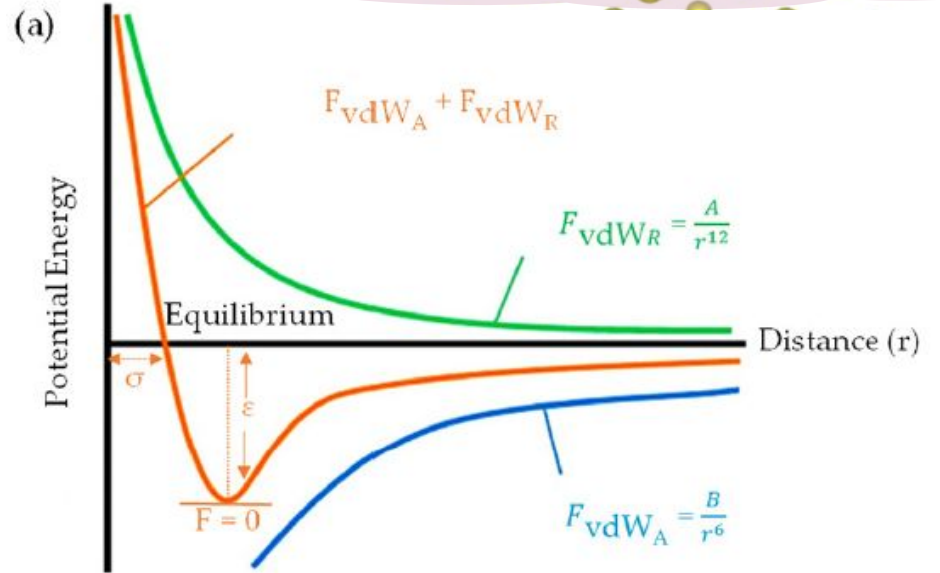
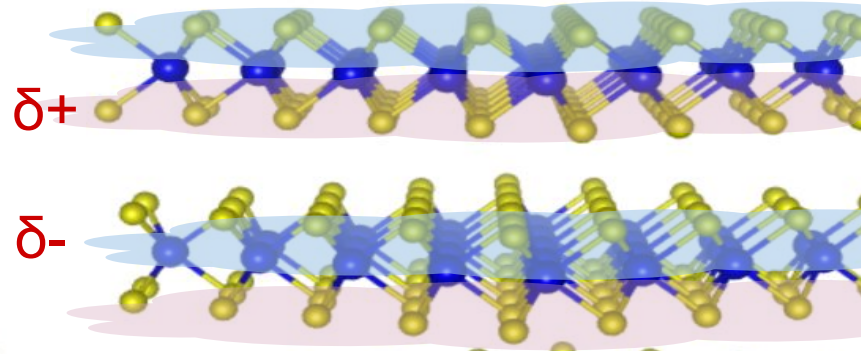
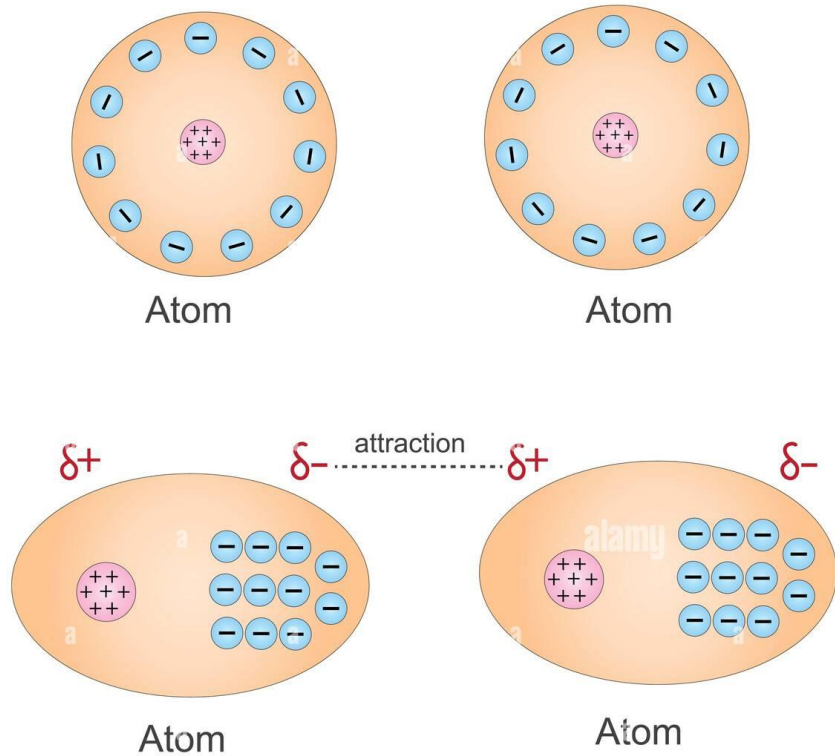
For elements with no stable isotopes, the mass number of the isotope with the longest half-life is in parentheses.

6	57	58	59	60	61	62	63	64	65	66	67	68	69	70	71
	La	Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu
	Lanthanum 138.91	Cerium 140.12	Praseodymium 140.91	Neodymium 144.24	Promethium (145)	Samarium 150.36	Europium 151.96	Gadolinium 157.25	Terbium 158.93	Dysprosium 162.50	Holmium 164.93	Erbium 167.26	Thulium 168.93	Ytterbium 173.05	Lutetium 174.97
7	89	90	91	92	93	94	95	96	97	98	99	100	101	102	103
	Ac	Th	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr
	Actinium (227)	Thorium 232.04	Protactinium 231.04	Uranium 238.03	Neptunium (237)	Plutonium (244)	Americium (243)	Curium (247)	Berkelium (247)	Californium (251)	Einsteinium (252)	Fermium (257)	Mendelevium (258)	Nobelium (259)	Lawrencium (266)





Van der Waals interactions



Naturally occurring van der Waals materials

Riccardo Frisenda¹, Yue Niu², Patricia Gant¹, Manuel Muñoz³ and Andres Castellanos-Gomez¹✉

The exfoliation of two naturally occurring van der Waals minerals, graphite and molybdenite, arouse

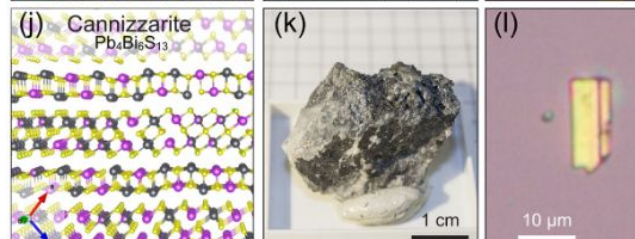
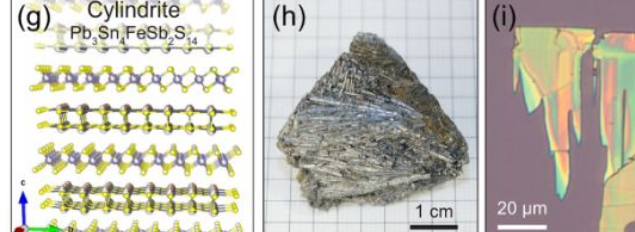
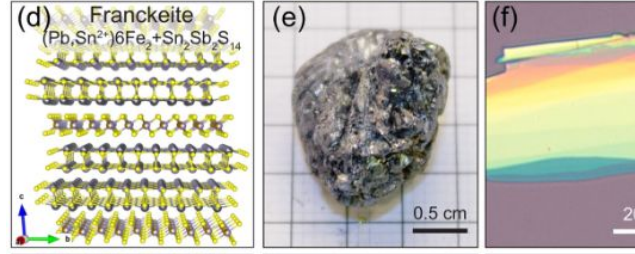
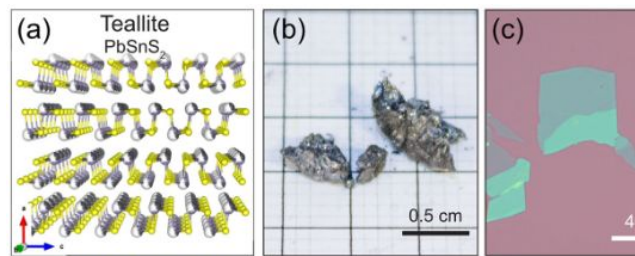
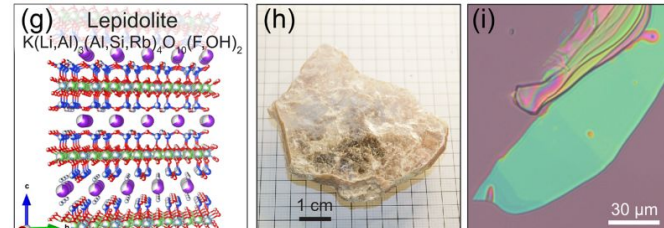
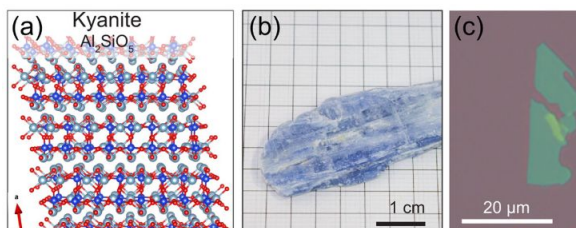
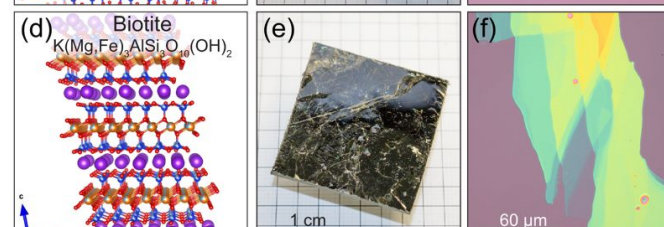
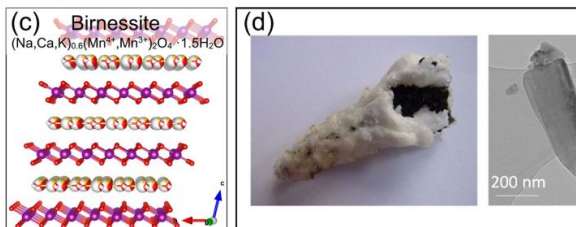
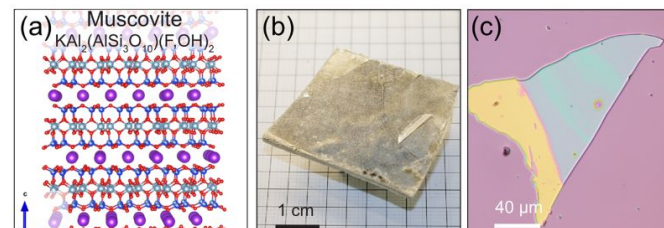
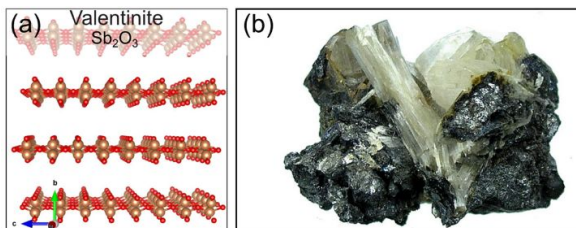
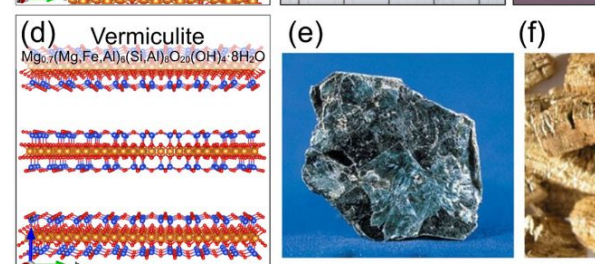
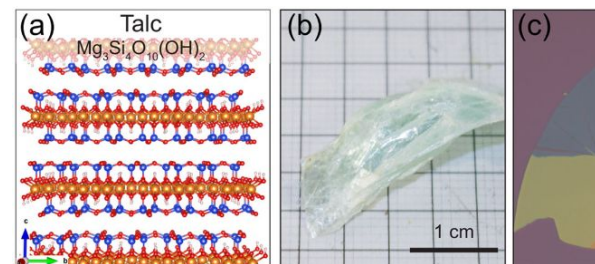
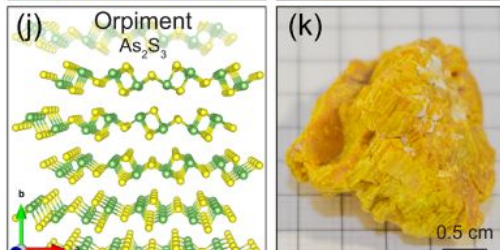
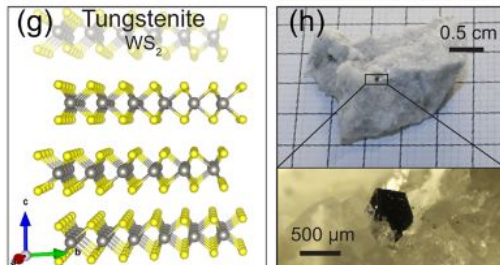
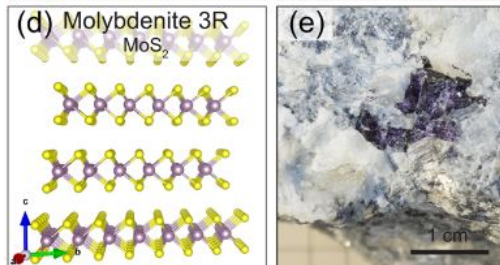
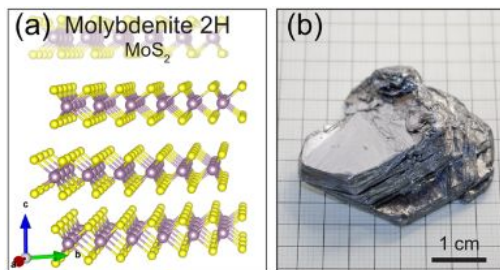
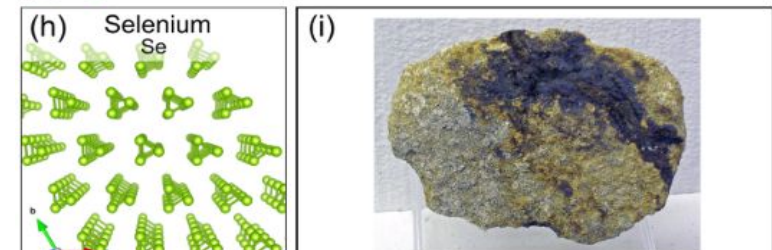
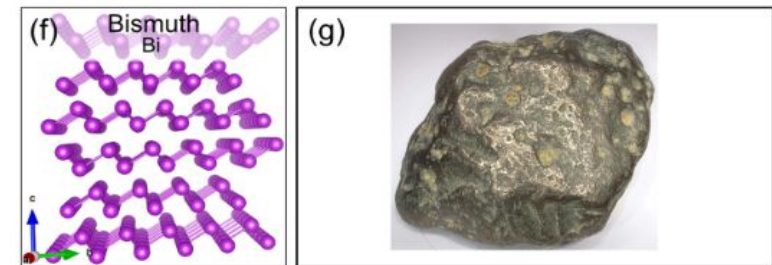
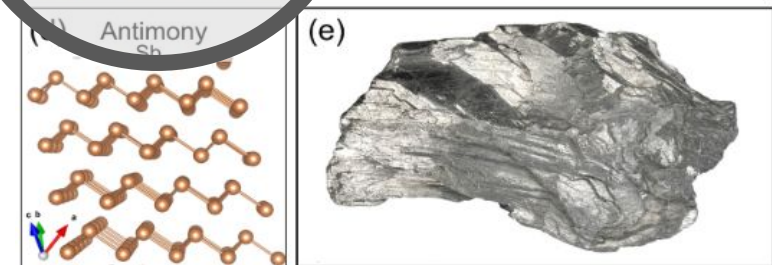
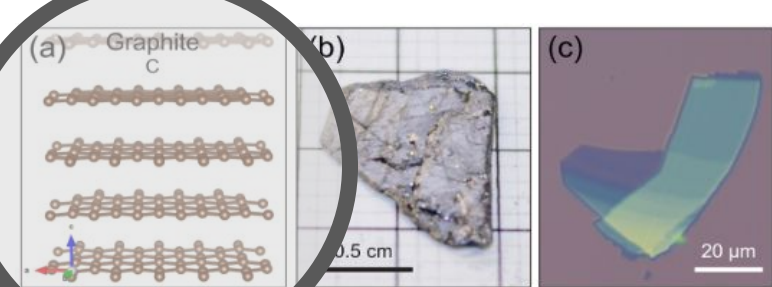
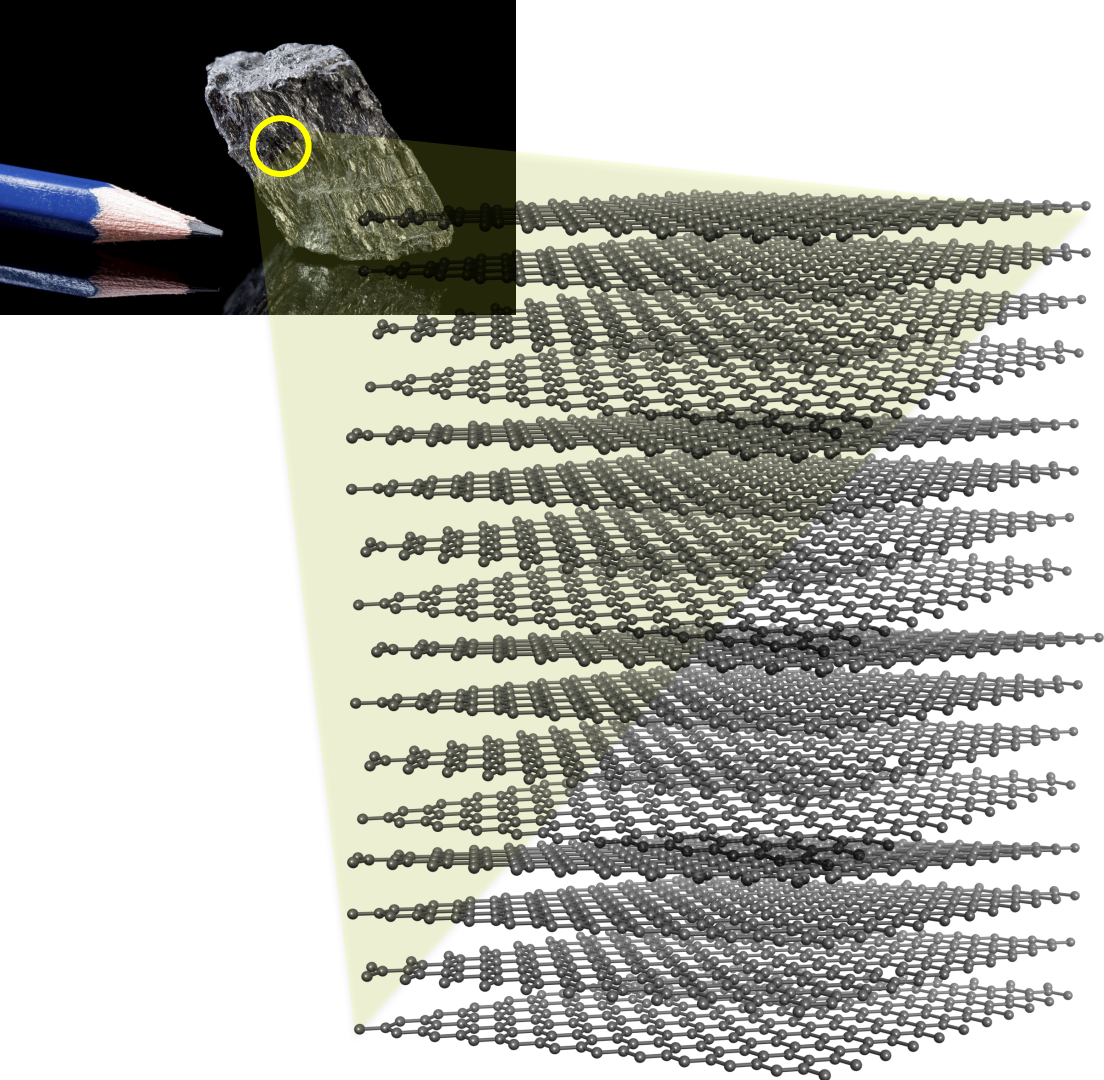


Figure showing the crystal structures and natural specimens of various van der Waals minerals. Each row corresponds to a different mineral, with (a) showing the crystal structure, (b) showing a photograph of a natural specimen, and (c) showing a false-color scanning electron micrograph (SEM) of the specimen. The minerals are: Valentinite (Sb_2O_3), Muscovite ($KAl_2(AlSi_3O_{10})(F,OH)_2$), Birnessite ($(Na,Ca,K)_{0.5}(Mn^{IV},Mn^{III})_2O_4 \cdot 1.5H_2O$), Biotite ($K(Mg,Fe)_3AlSi_3O_{10}(OH)_2$), Kyanite (Al_2SiO_5), Lepidolite ($K(Li,Al)(Al,Si,Rb)_4O_{10}(F,OH)_2$), Teallite ($PbSnS_3$), Franckeite ($(Pb,Sn)^{16}Fe_4+Sn_4Sb_{14}$), Cylindrite ($Pb_4Sn_4FeSb_4S_{24}$), and Cannizzarite ($Pb_4Bi_6S_{13}$).



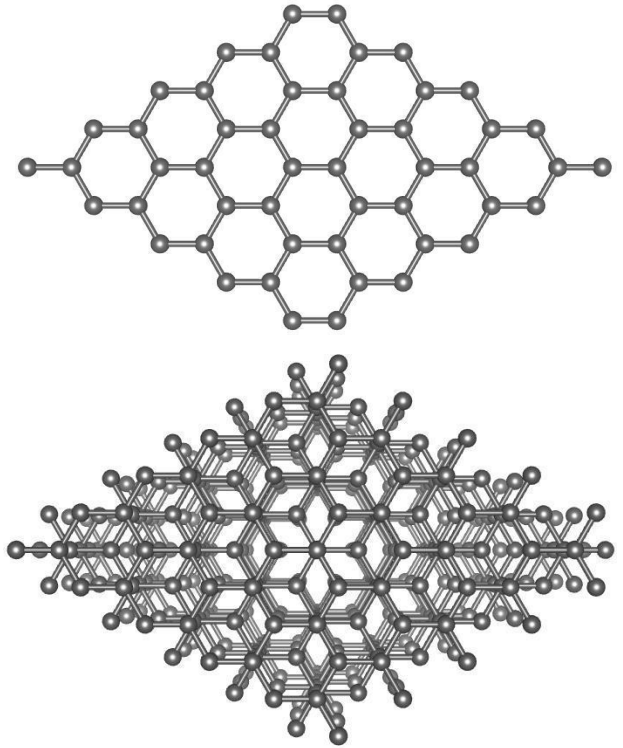


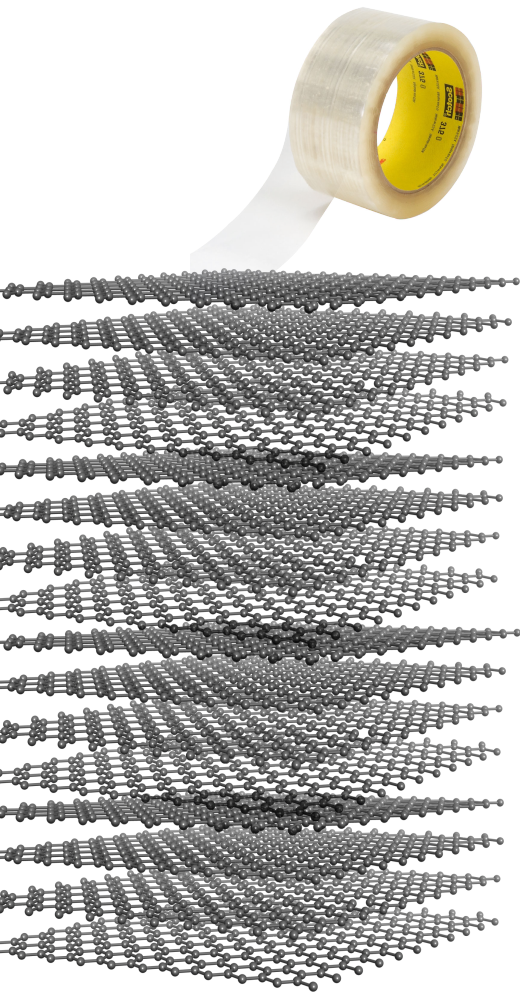
6

C

Carbon

12.011

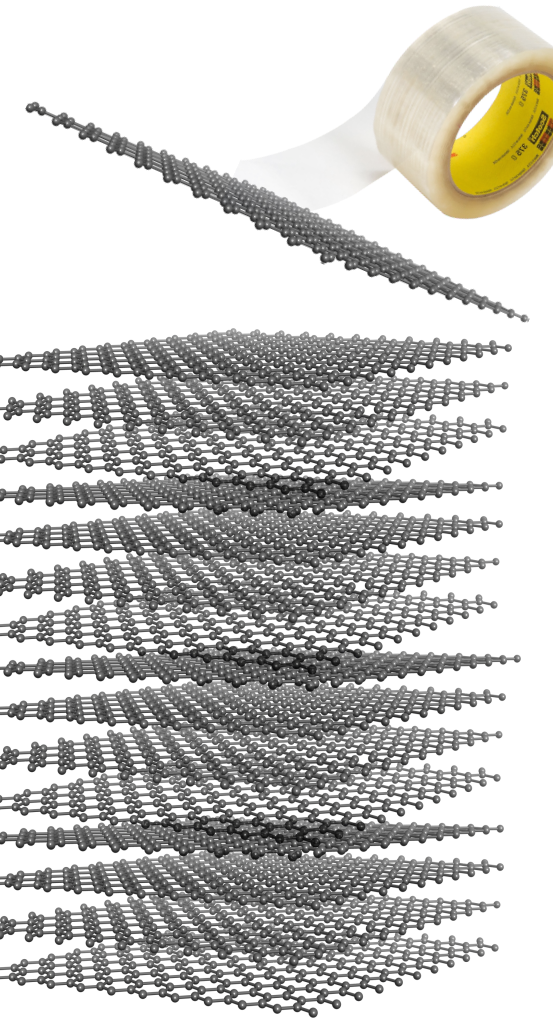




Electric Field Effect in Atomically Thin Carbon Films

K. S. Novoselov,¹ A. K. Geim,^{1*} S. V. Morozov,² D. Jiang,¹
Y. Zhang,¹ S. V. Dubonos,² I. V. Grigorieva,¹ A. A. Firsov²

We describe monocrystalline graphitic films, which are a few atoms thick but are nonetheless stable under ambient conditions, metallic, and of remarkably high quality. The films are found to be a two-dimensional semimetal with a tiny overlap between valence and conduction bands, and they exhibit a strong ambipolar



MANCHESTER
1824
The University of Manchester

Physics
2010



■ INTRODUCTION

The past decade has catalyzed the interest of the scientific community to study atomically thin materials (also known as two-dimensional (2D) materials). According to the Web of Science, the number of publications related to 2D materials have increased from ~1900 in 2004, when graphene was first isolated experimentally,¹ to ~49100 in 2021.² In that time, interest has expanded far beyond graphene. Other 2D

Yu Lei, et al. ACS Nanosci. Au, 2, 450, 2022.

Electric Field Effect in Atomically Thin Carbon Films

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We describe monocrystalline graphitic films, which are a few atoms thick but are nonetheless stable under ambient conditions, metallic, and of remarkably high quality. The films are found to be a two-dimensional semimetal with a tiny overlap between valence and conduction bands, and they exhibit a strong ambipolar

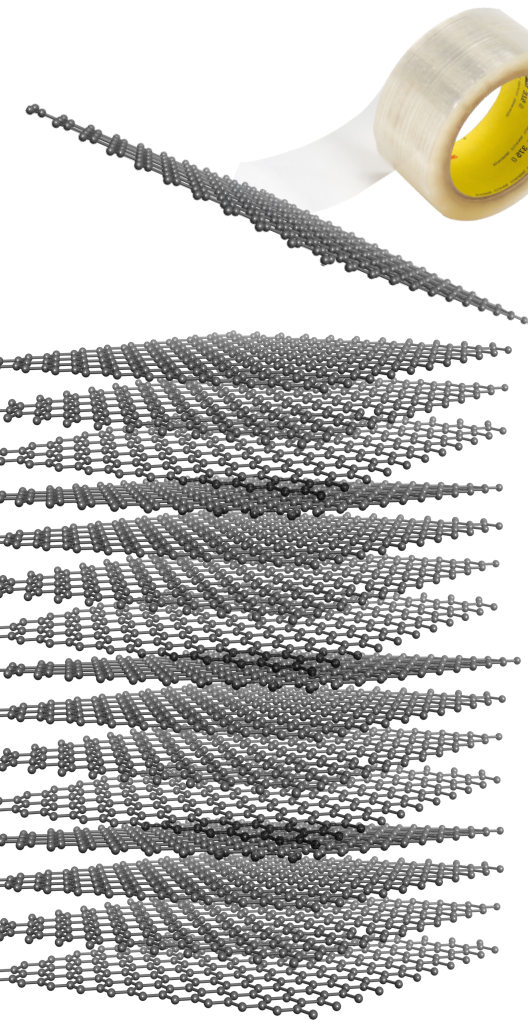
Experimental observation of the quantum Hall effect and Berry's phase in graphene

Yuanbo Zhang¹, Yan-Wen Tan¹, Horst L. Stormer^{1,2} & Philip Kim¹

When electrons are confined in two-dimensional materials, quantum-mechanically enhanced transport phenomena such as the quantum Hall effect can be observed. Graphene, consisting of an isolated single atomic layer of graphite, is an ideal realization of such a two-dimensional system. However, its behaviour is expected to differ markedly from the well-studied case of quantum wells in conventional semiconductor interfaces. This difference arises from the unique electronic properties of graphene, which

electron-like and hole-like carriers tuned by the electric field effect^{1,2,3,4}. However, the quantum Hall effect (QHE) was not observed in these samples, possibly as a result of their low mobility and/or the residual three-dimensional nature of the specimens.

The high-mobility graphene samples used in our experiments were extracted from Kish graphite (Toshiba Ceramics) on degenerately doped Si wafers with a 300-nm SiO₂ coating layer, by using micromechanical manipulation similar to that described in ref. 8.



Physics
2010

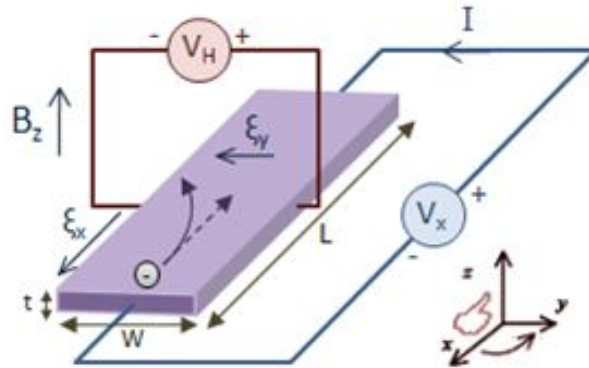
MANCHESTER
1824

The University of Manchester

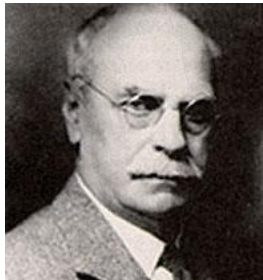


- **Thinnest.** At one atom thick, it's the thinnest material we can see.
- **Lightest.** One square meter of graphene weighs about 0.77 milligrams. For scale, one square meter of regular paper is 1000 times heavier than graphene and a single sheet of graphene big enough to cover a football field would weigh less than a gram.
- **Strongest.** Graphene is stronger than steel and Kevlar, with a tensile strength of 150,000,000 psi.
- **Stretchiest.** Graphene has an amazing ability to retain its initial size after strain. Graphene sheets suspended over silicone dioxide cavities had spring constants in the region of 1-5 N/m and a Young's modulus of 0.5 TPa.
- **Best Conductor of Heat.** At room temperature, graphene's heat conductivity is $(4.84 \pm 0.44) \times 10^3$ to $(5.30 \pm 0.48) \times 10^3$ W·m⁻¹·K⁻¹.
- **Best Conductor of Electricity.** In graphene, each carbon atom is connected to three other carbon atoms on a two-dimensional plane, which leaves one electron free for electronic conduction. Recent studies have shown electron mobility at values more than 15,000 cm²·V⁻¹·s⁻¹. Graphene moves electrons 10 times faster than silicon using less energy.
- **Best Light Absorber.** Graphene can absorb 2.3% of white light, which is remarkable because of its extreme thinness. This means that, once optical intensity reaches saturation fluence, saturable absorption takes place, which makes it possible to achieve full-band mode locking.
- **Most Renewable.** Statistically speaking, carbon is the fourth most abundant element in the entire universe (by mass). Because of this abundance, graphene could well be a sustainable, ecologically friendly solution for an increasingly complex world.
- **Most Exceptional.** What most captures the imagination is that graphene is one simple material that by itself possesses all these astonishing qualities. No other material in the world is the thinnest, strongest, lightest, and stretchiest, and can conduct heat and electricity super-fast, all at the same time.

Hall Effect

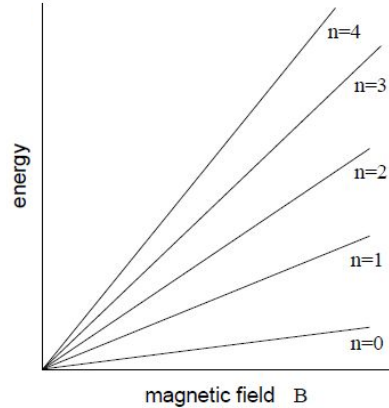


$$\mathbf{F} = q(\mathbf{E} + \mathbf{v} \times \mathbf{B})$$



Edwin Herbert Hall
(1879)

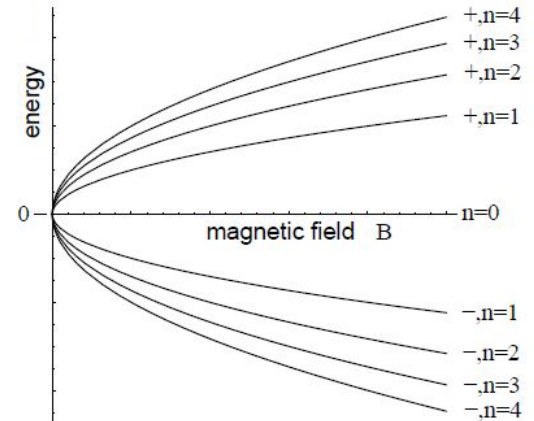
Quantum Hall Effect



$$\epsilon_n = \hbar\omega_C(n + 1/2)$$

$$\propto B(n + 1/2)$$

Anomalous Quantum Hall Effect



$$\epsilon_{\lambda,n} = \lambda(\hbar v/l_B)\sqrt{2n}$$

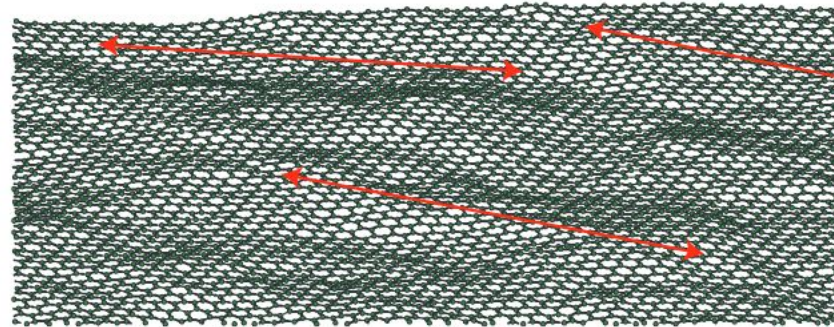
$$\propto \lambda\sqrt{Bn}$$

Intrinsic ripples in graphene

A. FASOLINO*, J. H. LOS AND M. I. KATSNELSON

Institute for Molecules and Materials, Radboud University Nijmegen, Toernooiveld 1, 6525ED Nijmegen, The Netherlands

*e-mail: a.fasolino@science.ru.nl



The stability of two-dimensional (2D) layers and is the subject of a long-standing theoretical debate

to the so-called Mermin–Wagner theorem¹, long-wavelength fluctuations destroy the long-range order of 2D crystals.

Similarly, 2D membranes embedded in a 3D space have a tendency to be crumpled². These fluctuations can, however, be suppressed by anharmonic coupling between bending and stretching modes meaning that a 2D membrane can exist but will exhibit strong height fluctuations^{2–4}. The discovery of

Figure 1 A representative configuration of the $N = 8,640$ sample

The red arrows are ~ 80 Å long.

Two-dimensional atomic crystals

K. S. Novoselov*, D. Jiang*, F. Schedin*, T. J. Booth*, V. V. Khotkevich*, S. V. Morozov[†], and A. K. Geim**[‡]

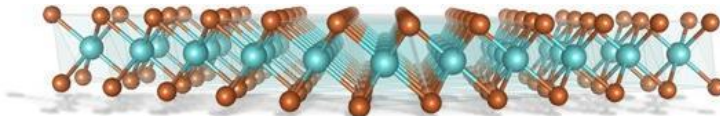
*Centre for Mesoscience and Nanotechnology and School of Physics and Astronomy, University of Manchester, Manchester M13 9PL, United Kingdom; and [†]Institute for Microelectronics Technology, Chernogolovka 142432, Russia

Edited by T. Maurice Rice, Swiss Federal Institute of Technology, Zurich, Switzerland, and approved June 7, 2005 (received for review April 6, 2005)

We report free-standing atomic crystals that are strictly 2D and can be viewed as individual atomic planes pulled out of bulk crystals or as unrolled single-wall nanotubes. By using micromechanical cleavage, we have prepared and studied a variety of 2D crystals including single layers of boron nitride, graphite, several dichalcogenides, and complex oxides. These atomically thin sheets (essentially gigantic 2D molecules unprotected from the immediate environment) are stable under ambient conditions, exhibit high crystal quality, and are continuous on a macroscopic scale.

wafer (Fig. 1d), because even a monolayer adds up sufficient to the optical path of reflected light so that the interference color changes with respect to the one of an empty substrate (photocontrast). The whole procedure takes literally half an hour to implement and identify probable 2D crystallites. Their further analysis was done by atomic force microscopy (AFM), for which single-layer crystals were selected as those exhibiting an apparent (12) thickness of approximately the interlayer distance in corresponding 3D crystals.

Transition Metal Dichalcogenides (TMDCs)



MX_2

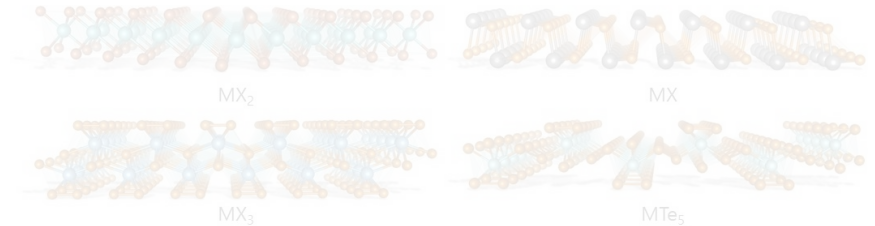
Materiais ~~bidimensionais~~ atômicamente finos

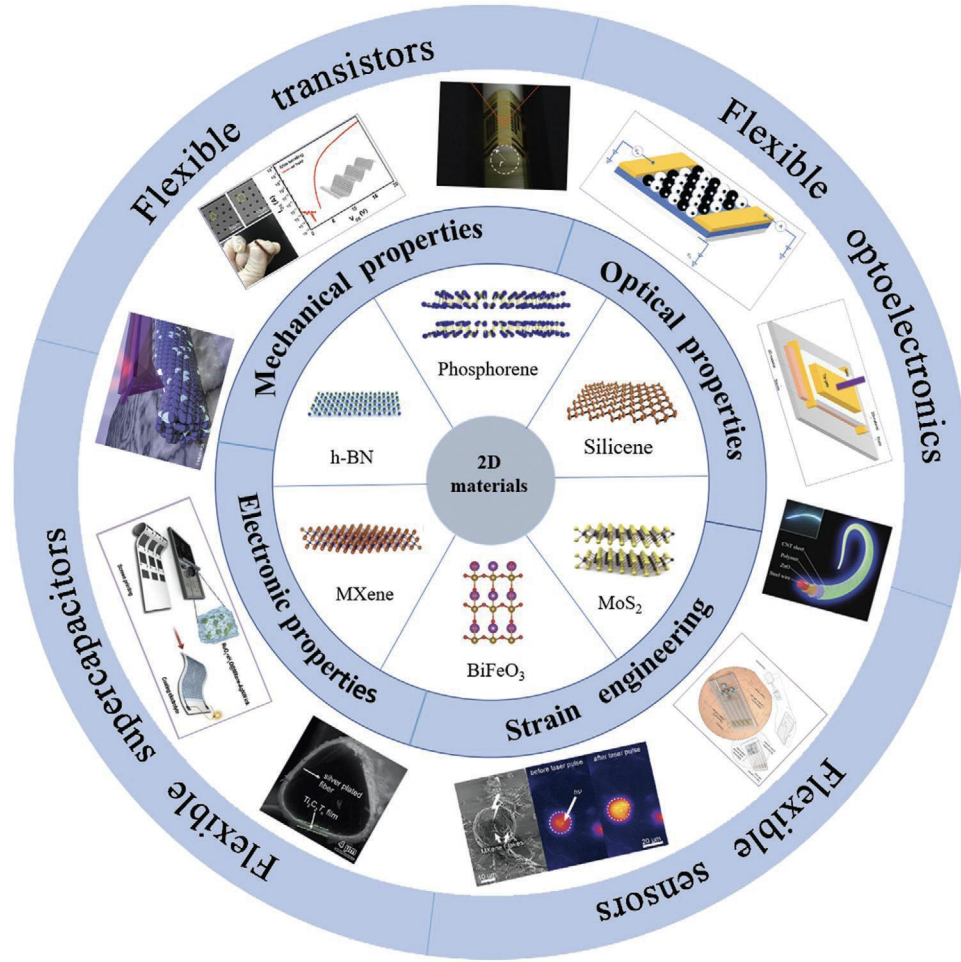
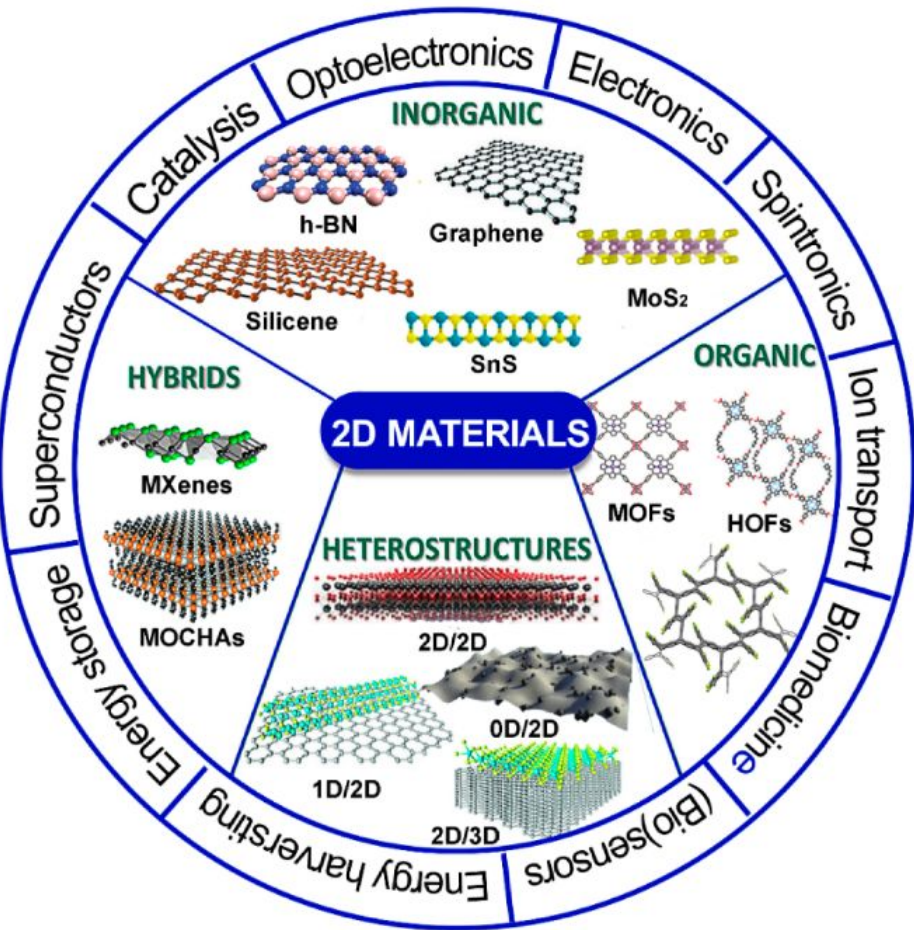
O que são?

Cristais com um ou poucos átomos de espessura

Interações eletrônicas no plano são muito mais fortes do que aquelas na direção perpendicular ao plano.

Para que servem?





2D materials for quantum information science

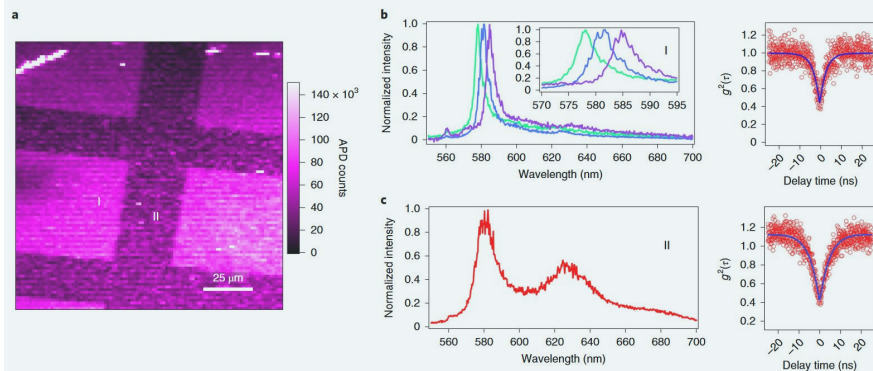
Xiaolong Liu¹ and Mark C. Hersam^{1,2,3,4*}

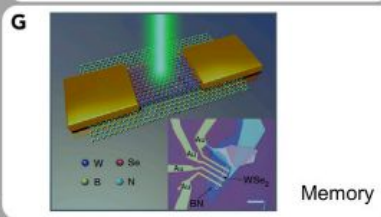
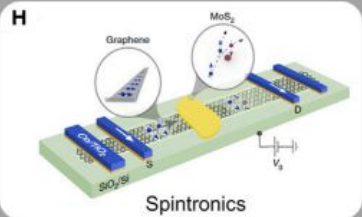
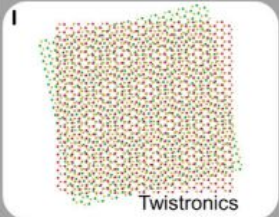
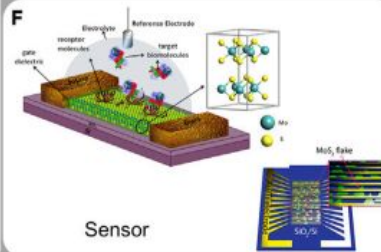
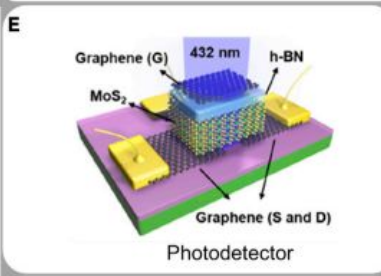
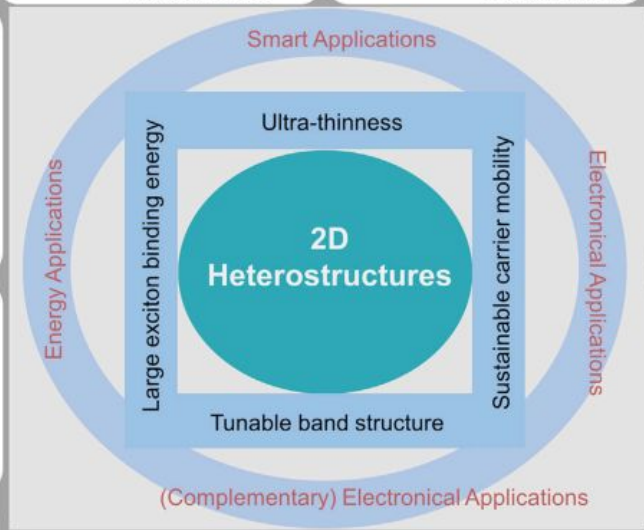
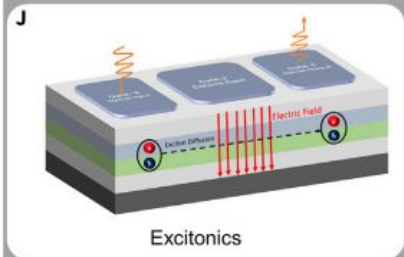
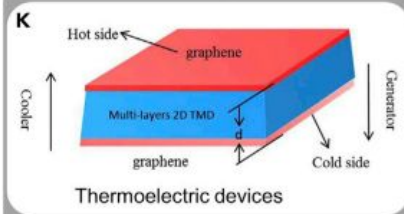
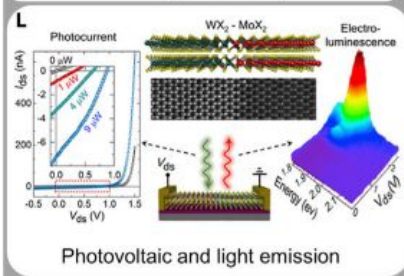
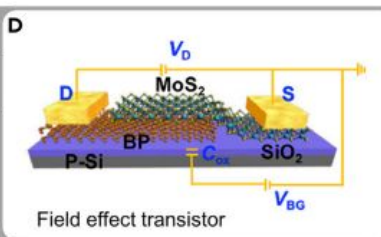
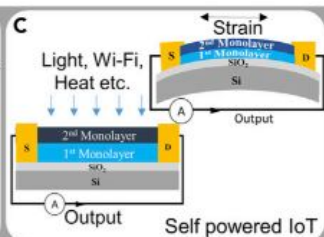
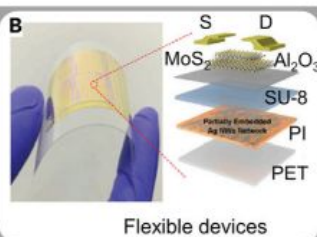
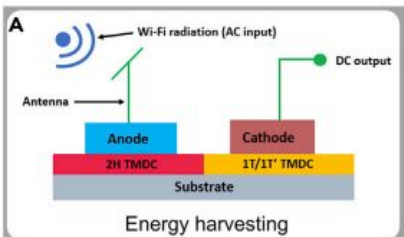
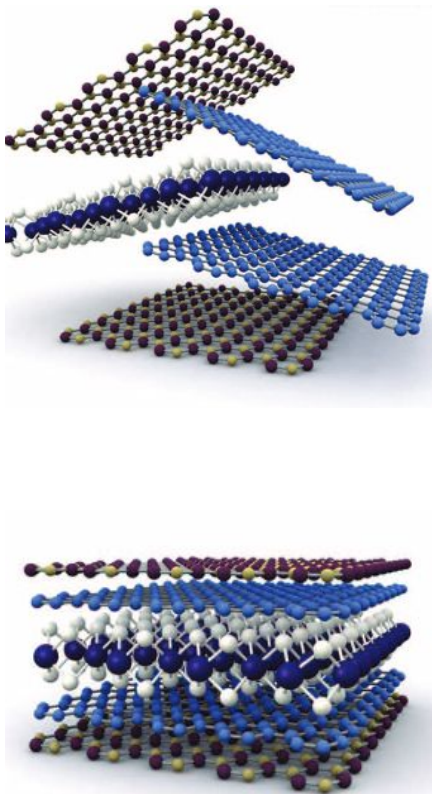
Abstract | The transformation of digital computers from bulky machines to portable systems has been enabled by new materials and advanced processing technologies that allow ultr

Identifying carbon as the source of visible single-photon emission from hexagonal boron nitride

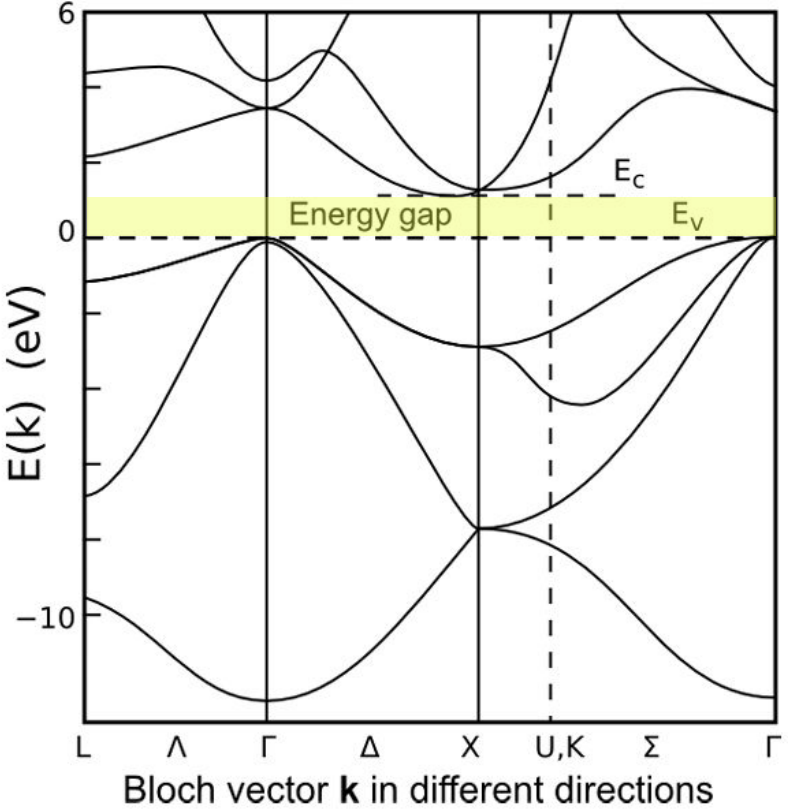
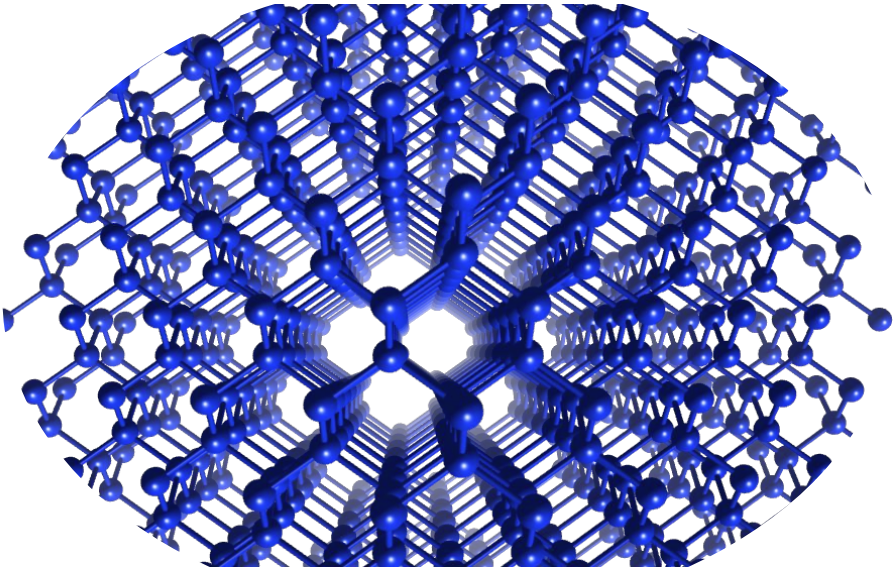
Noah Mendelson¹, Dipankar Chugh², Jeffrey R. Reimers^{1,3}, Tin S. Cheng⁴, Andreas Gottscholl⁵, Hu Long^{6,7,8}, Christopher J. Mellor⁴, Alex Zettl^{6,7,8}, Vladimir Dyakonov⁵, Peter H. Beton⁴, Sergei V. Novikov⁴, Chennupati Jagadish^{2,9}, Hark Hoe Tan^{2,9}, Michael J. Ford¹, Milos Toth^{1,10}, Carlo Bradac^{1,11} and Igor Aharonovich^{1,10,5,23}

Single-photon emitters (SPEs) in hexagonal boron nitride (hBN) have garnered increasing attention over the last few years due to their superior optical properties. However, despite the vast range of experimental results and theoretical calculations, the defect structure responsible for the observed emission has remained elusive. Here, by controlling the laser properties of laser-

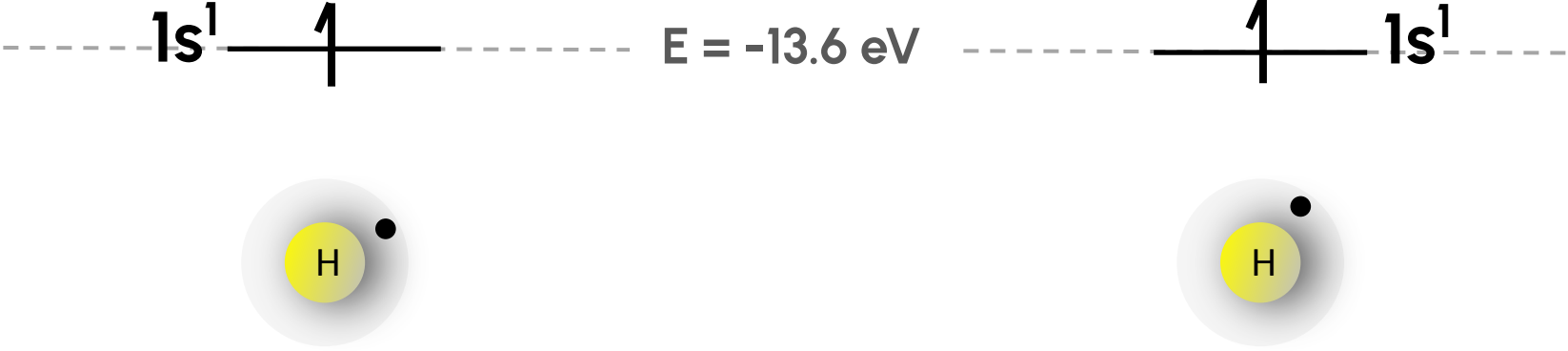




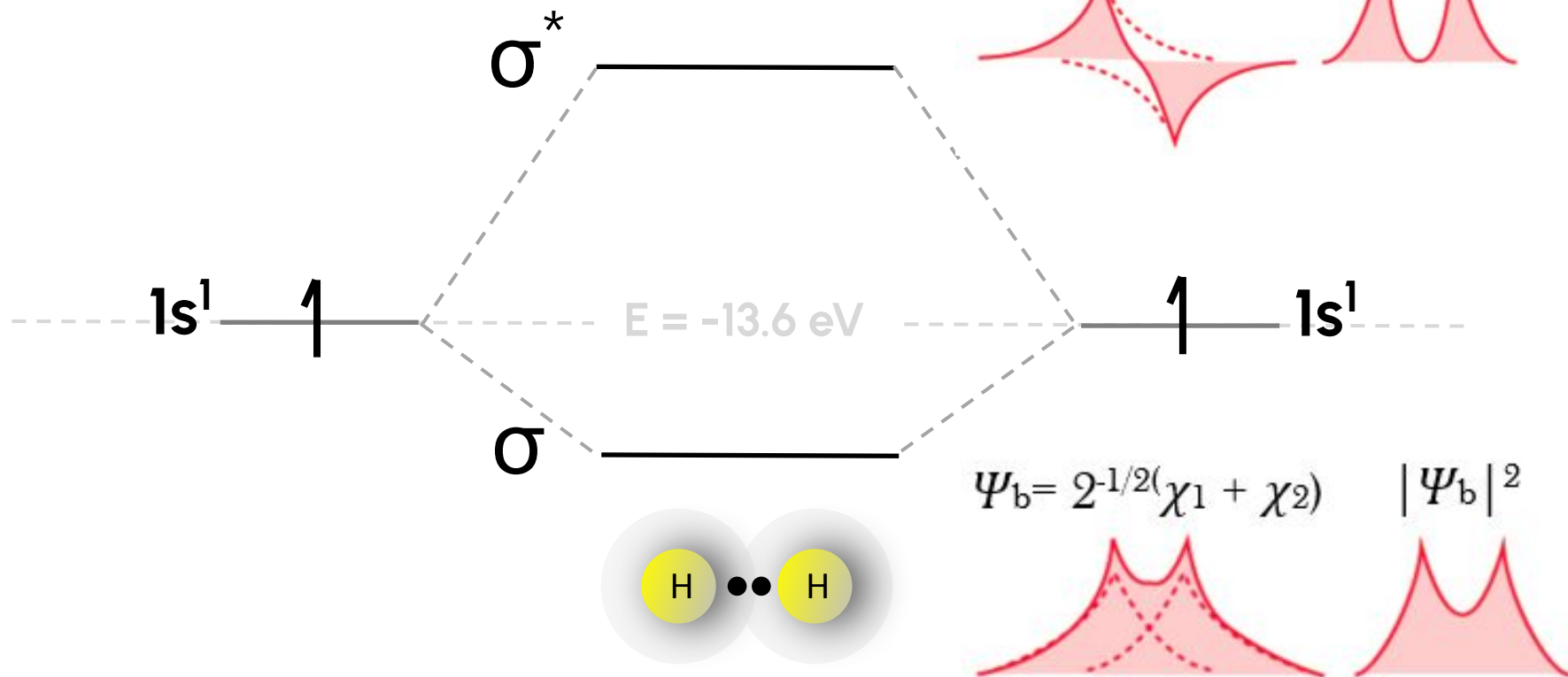
Electronic Band Structure



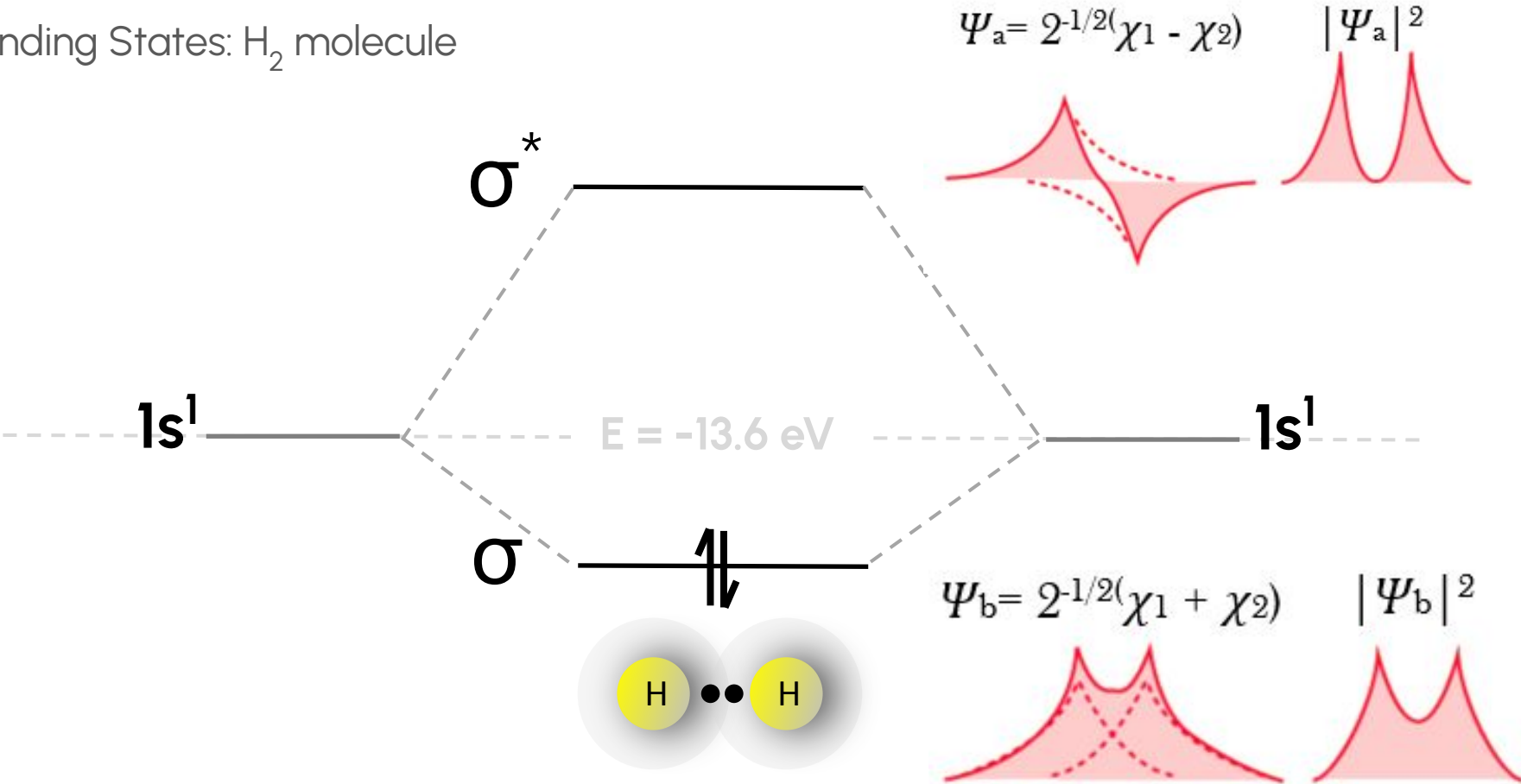
Bonding States: H₂ molecule



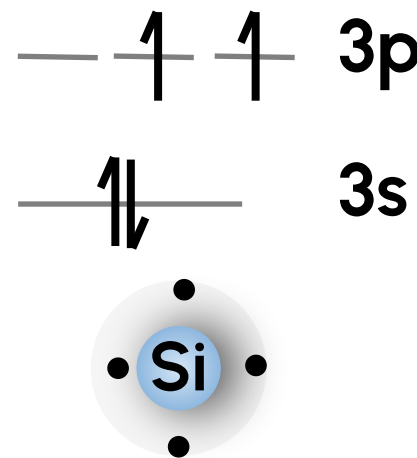
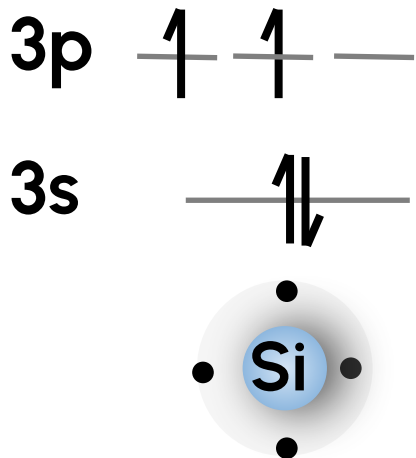
Bonding States: H₂ molecule



Bonding States: H₂ molecule



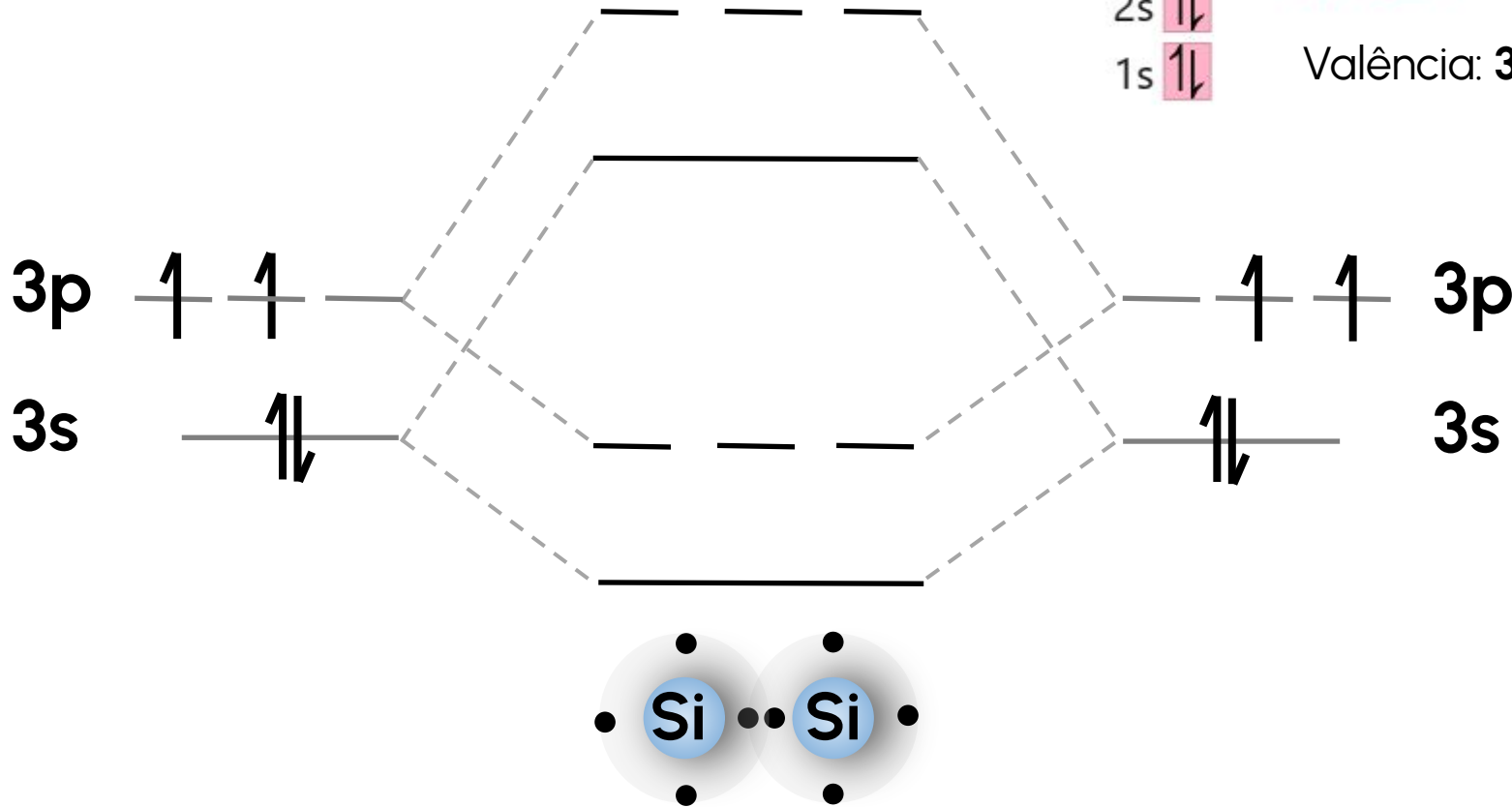
Electronic Band Structure: Si crystal



Electronic Band Structure: Si crystal

5s		4p				14 Si Silicon 28.085
4s		3p	↑	↑		
3s	↑↓	2p	↑↓	↑↓	↑↓	
2s	↑↓					
1s	↑↓					

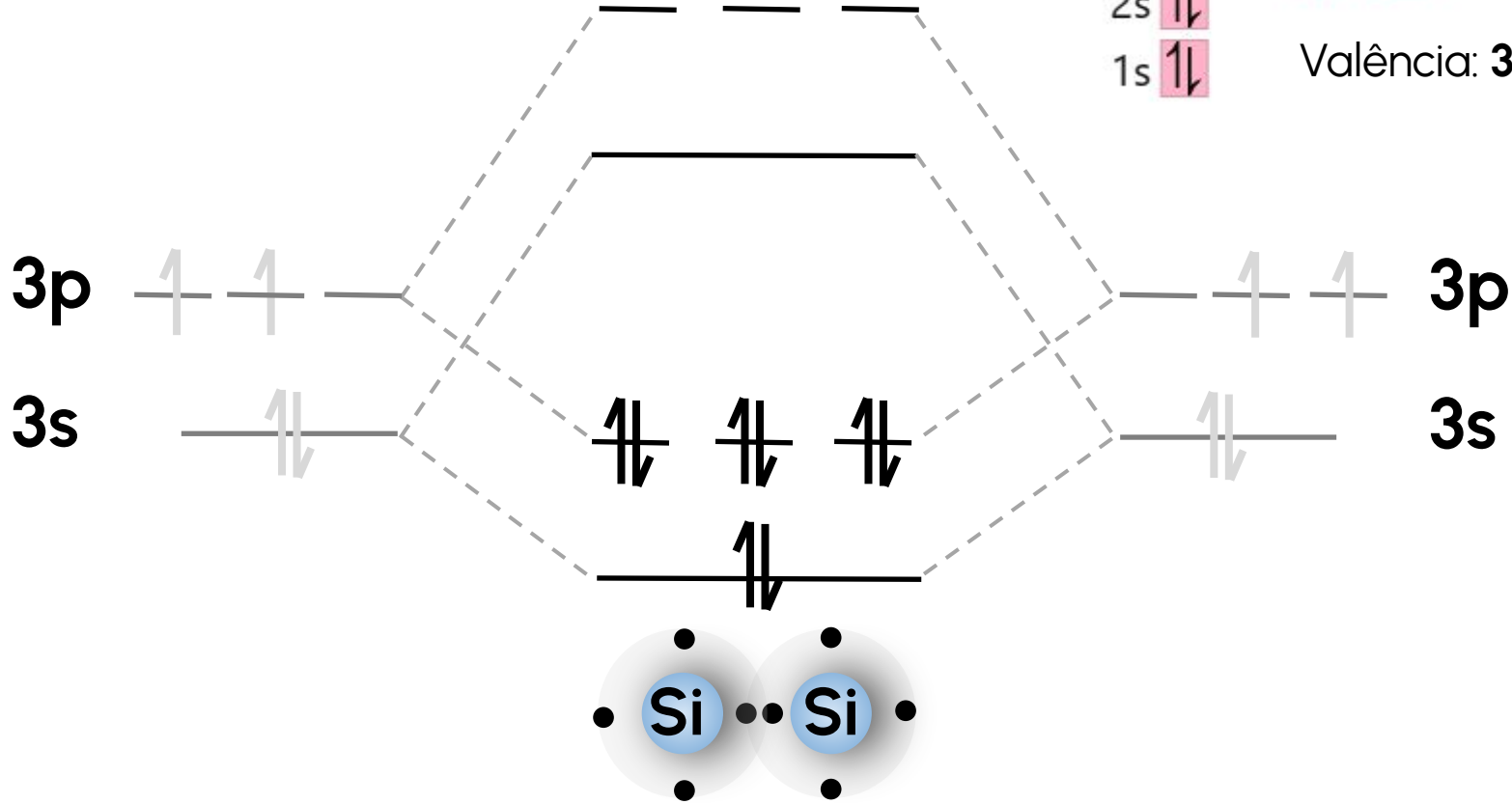
Valência: $3s^2 3p^2$



Electronic Band Structure: Si crystal

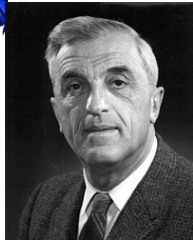
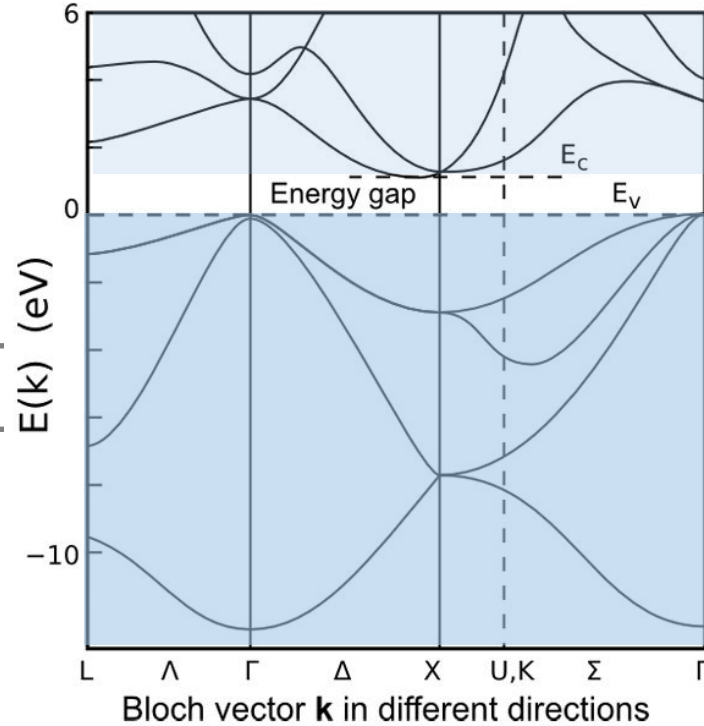
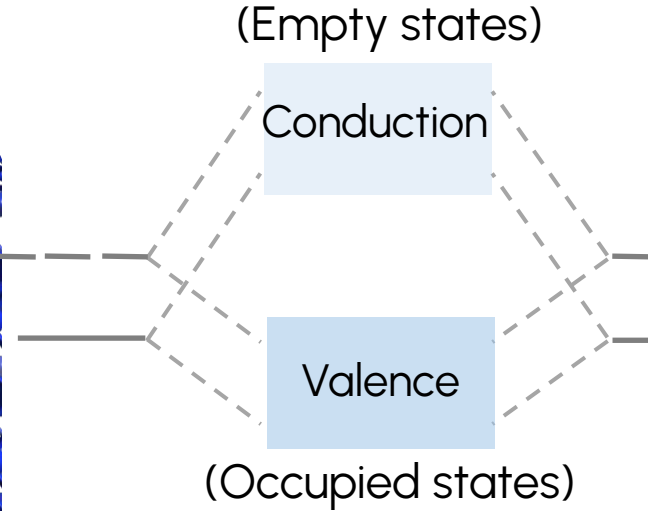
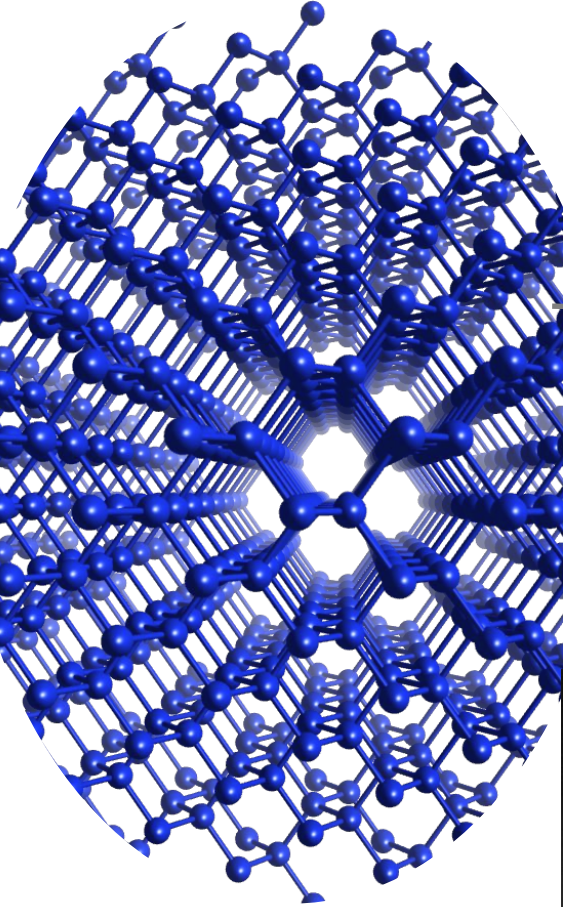
5s		4p			14 Si Silicon 28.085	
4s		3p	↑	↑		
3s	↑↓	2p	↑↓	↑↓		↑↓
2s	↑↓					
1s	↑↓					

Valência: $3s^2 3p^2$



Electronic Band Structure: Si crystal

If we have a lot of atoms? ($\sim 10^{23}$)



Felix Bloch
(1905-1983)

Bloch's Theorem

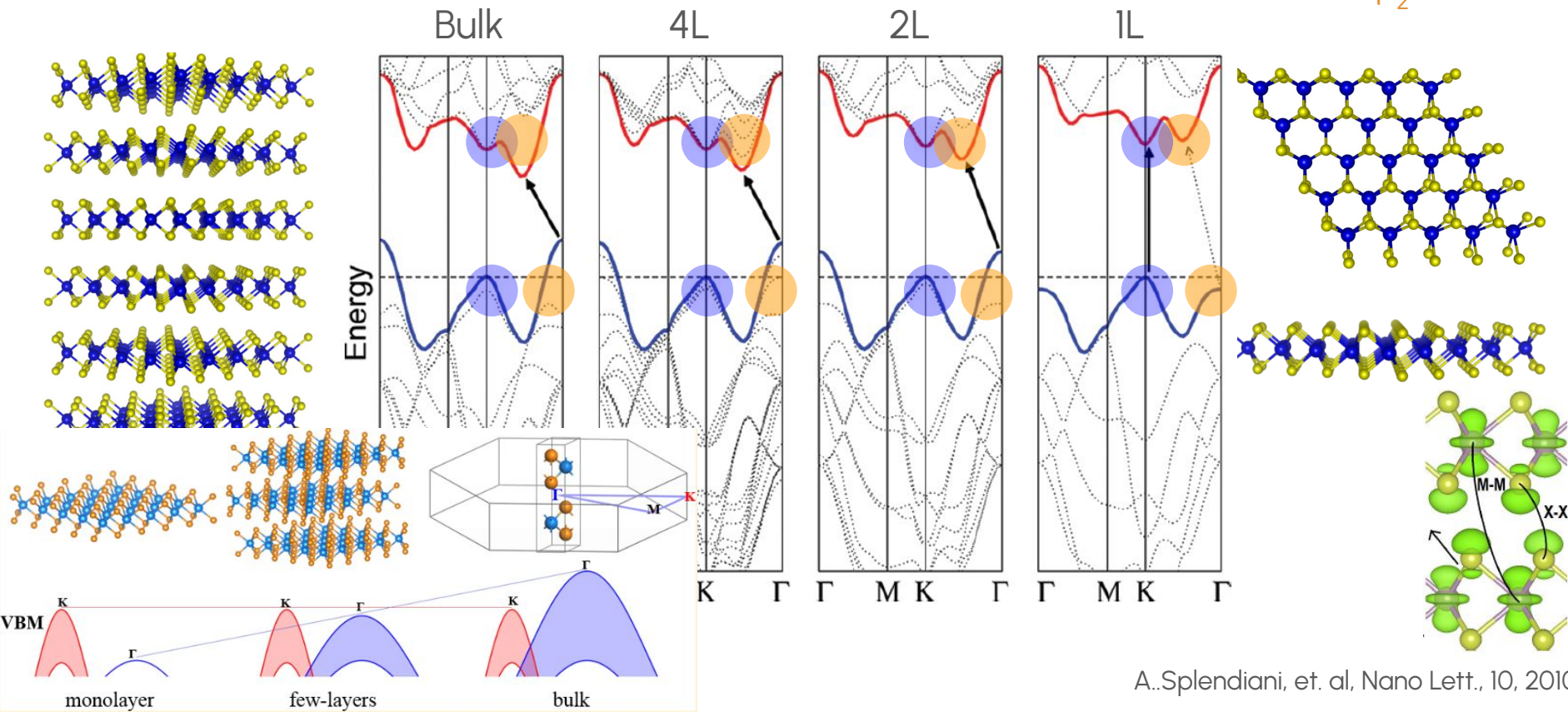
$$\psi(\mathbf{r}) = e^{i\mathbf{k}\cdot\mathbf{r}} u(\mathbf{r})$$

Band Gap Tuning: TMDCs

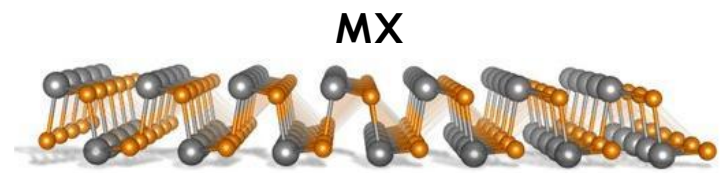
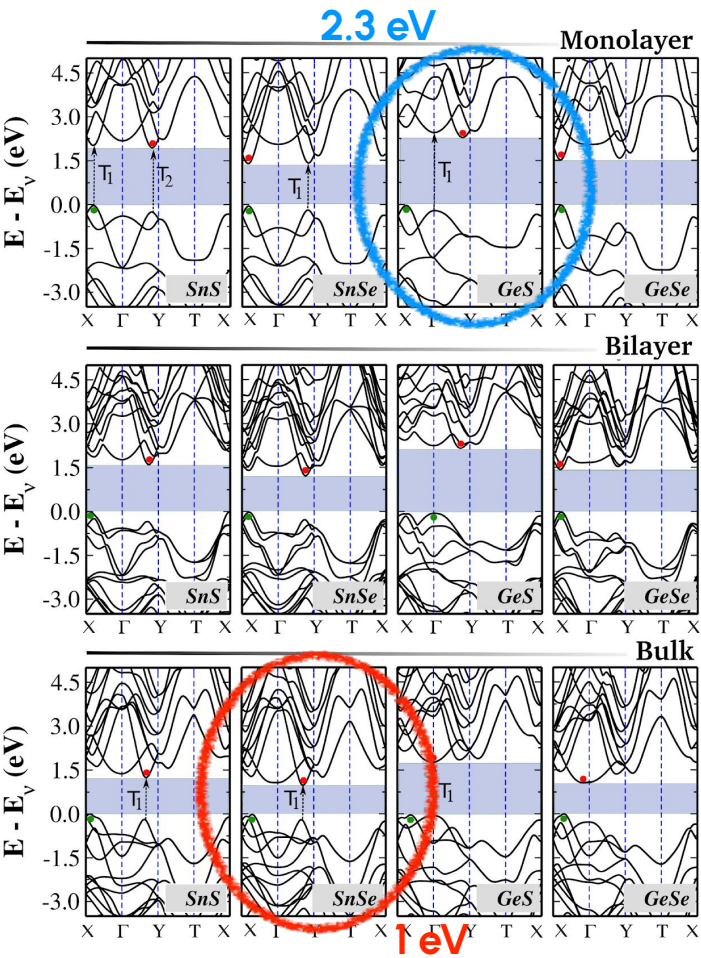
TX_2

MoS_2

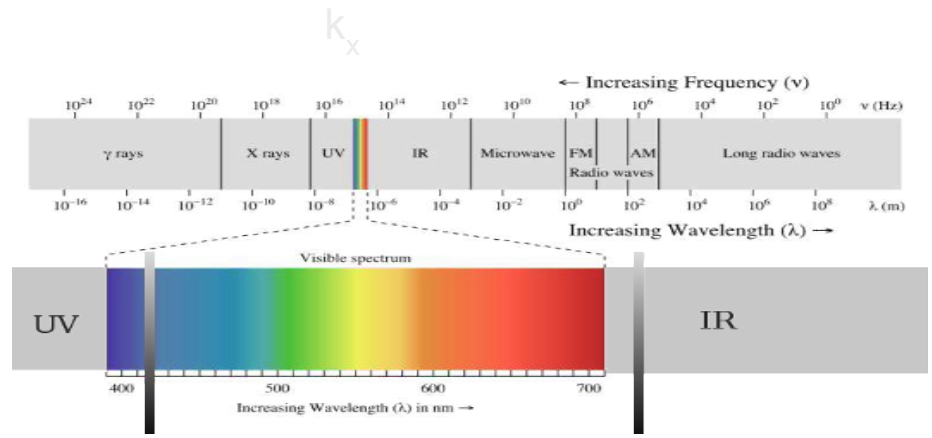
Mo-d
Mo-d + S-p_z



Band Gap Tuning: Group-IV Monochalcogenides



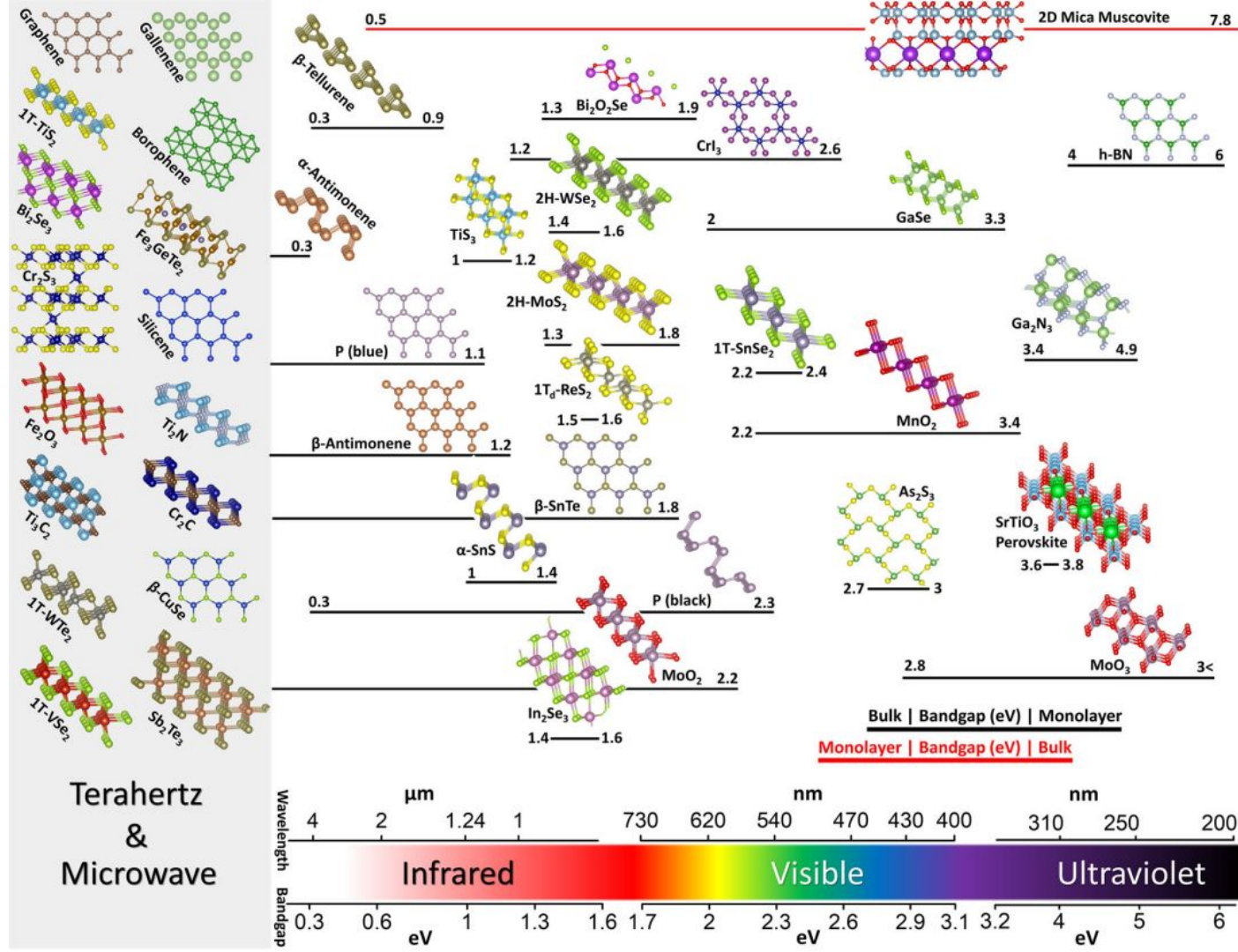
M = Sn, Ge, X = S, Se



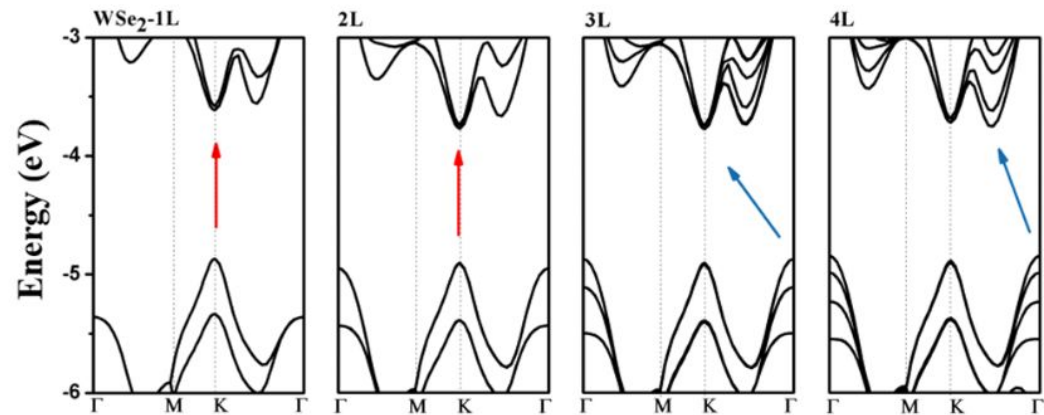
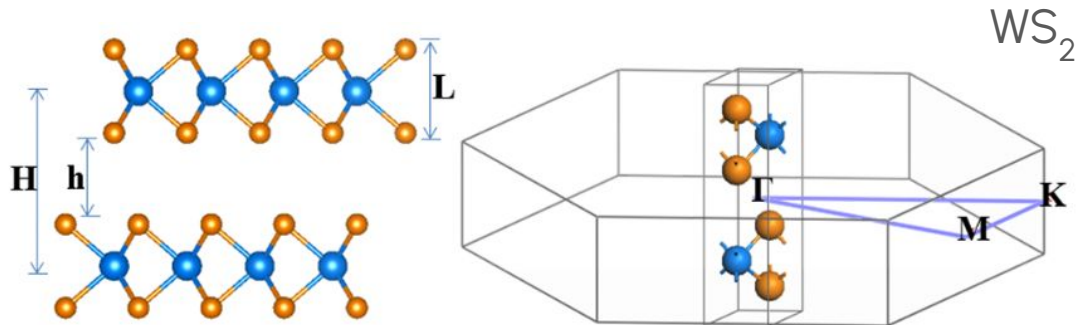
2D GeS

3D SnSe

Gaps de energia cobrindo toda a região do visível.



Band Gap Tuning: TMDCs

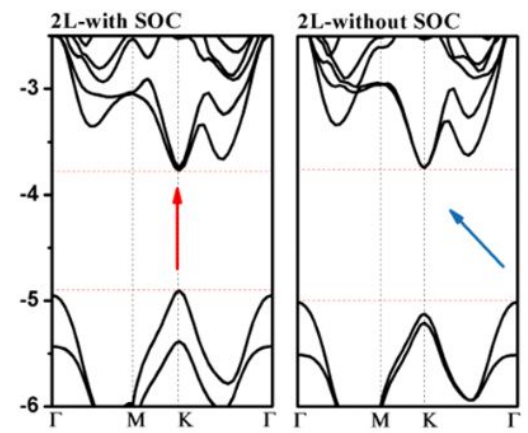
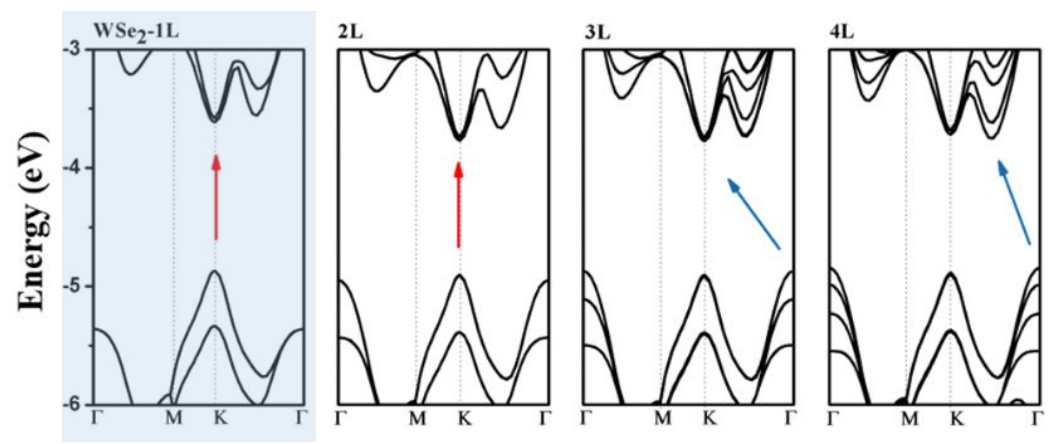
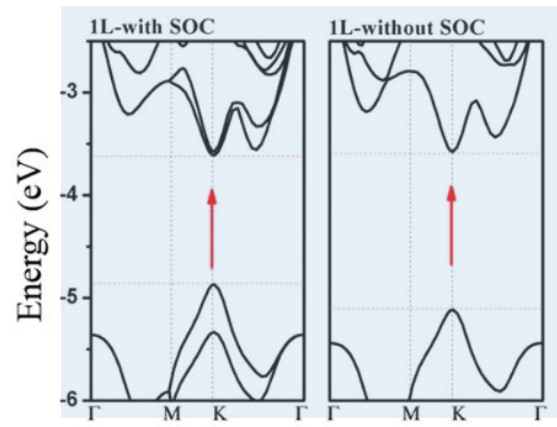
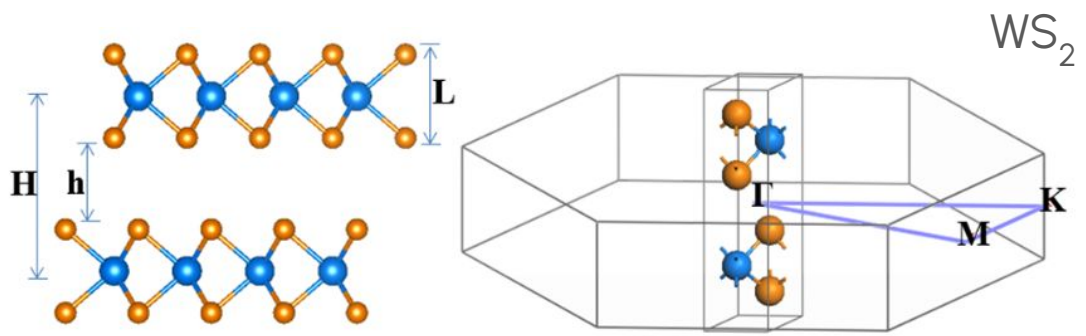


Spin Orbit Coupling (SOC)

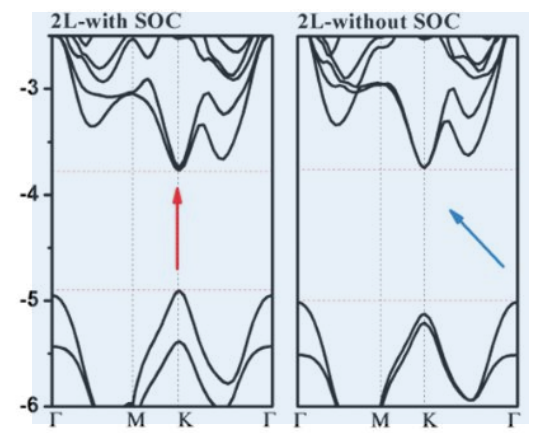
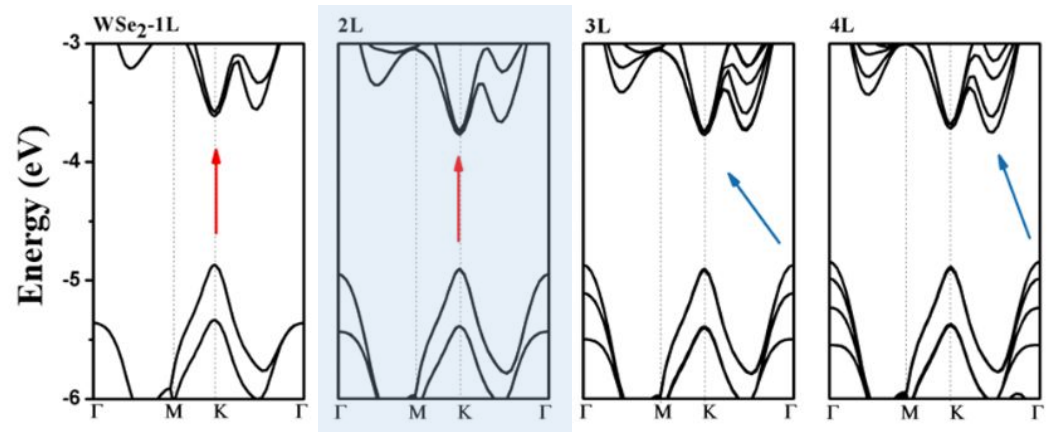
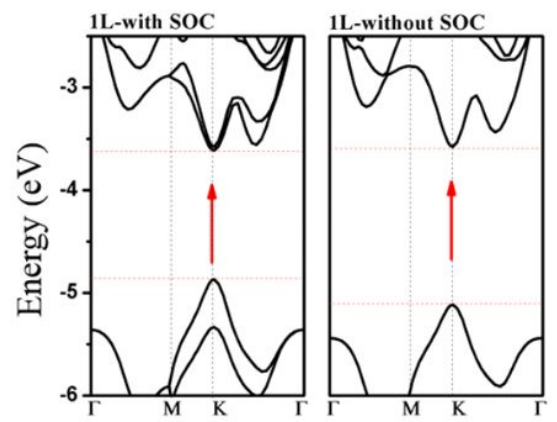
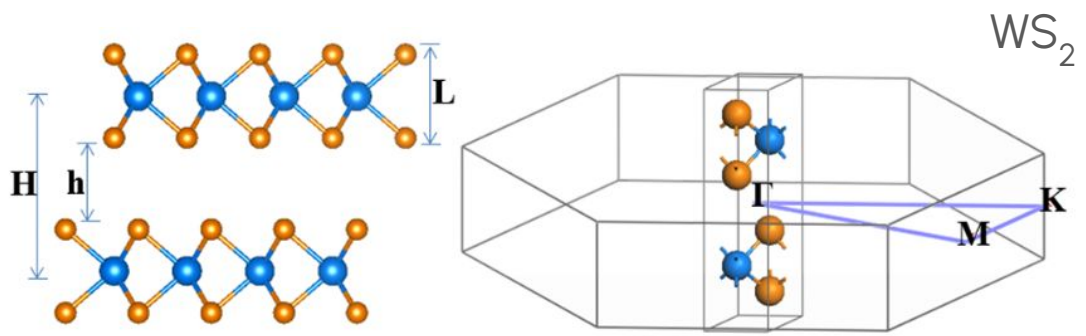
Relativistic interaction of a particle's spin with its motion inside a potential.

$$H_{SO} = \frac{1}{2m_e^2c^2} \frac{1}{r} \frac{dV(r)}{dr} \vec{S} \cdot \vec{L}$$

Band Gap Tuning: TMDCs



Band Gap Tuning: TMDCs



spin transport electronics

REVIEW

Spintronics: A Spin-Based Electronics Vision for the Future

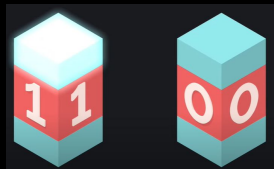
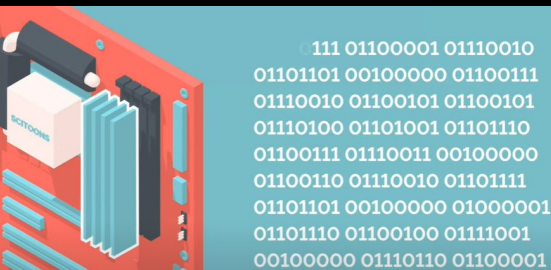
S. A. Wolf,^{1,2*} D. D. Awschalom,³ R. A. Buhrman,⁴ J. M. Daughton,⁵ S. von Molnár,⁶ M. L. Roukes,⁷ A. Y. Chtchelkanova,⁸ D. M. Treger⁸

This review describes a new paradigm of electronics based on the spin degree of freedom of the electron. Either adding the spin degree of freedom to conventional charge-based electronic devices or using the spin alone has the potential advantages of nonvolatility, increased data pro-

duced power consumption, and increased speed, compared with conventional semiconductor devices.

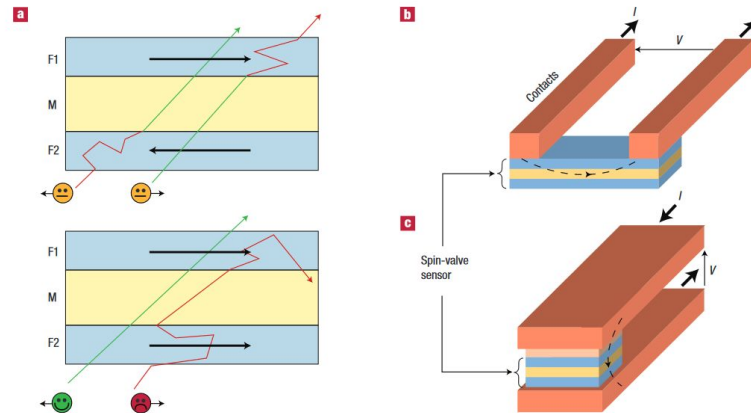
Major challenges in this field of spintronics that are addressed by experiment and

Electronics




The emergence of spin electronics in data storage

Electrons have a charge and a spin, but until recently these were considered separately. In classical electronics, charges are moved by electric fields to transmit information and are stored in a capacitor to save it. In magnetic recording, magnetic fields have been used to read or write the information stored on the magnetization, which 'measures' the local orientation of spins in ferromagnets. The picture started to change in 1988, when the discovery of giant

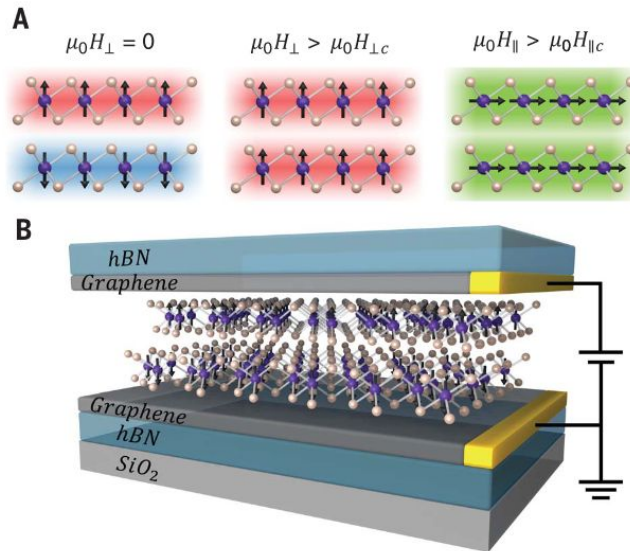


REVIEW ARTICLE OPEN

2D materials for spintronic devices

Ethan C. Ahn  ¹✉

2D materials are attractive for nanoelectronics due to their ultimate thickness dimension and variety of emerging spintronic device concepts will greatly benefit from the use of 2D material manipulating spin. In this review, we discuss various 2D materials, including graphene and other



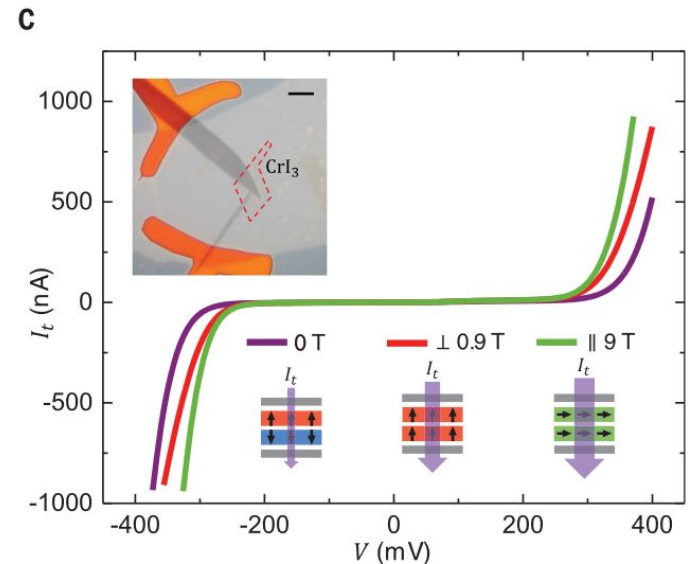
RESEARCH

MAGNETISM

Giant tunneling magnetoresistance in spin-filter van der Waals heterostructures

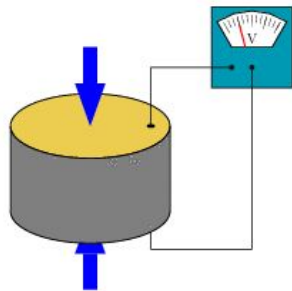
Tiancheng Song^{1*}, Xinghan Cai^{1*}, Matisse Wei-Yuan Tu², Xiaou Zhang³, Bevin Huang¹, Nathan P. Wilson¹, Kyle L. Seyler¹, Lin Zhu⁴, Takashi Taniguchi⁵, Kenji Watanabe⁵, Michael A. McGuire⁶, David H. Cobden¹, Di Xiao^{2,†}, Wang Yao^{2,†}, Xiaodong Xu^{1,4,†}

Magnetic multilayer devices that exploit magnetoresistance are the backbone of magnetic sensing and data storage technologies. Here, we report multiple-spin-filter

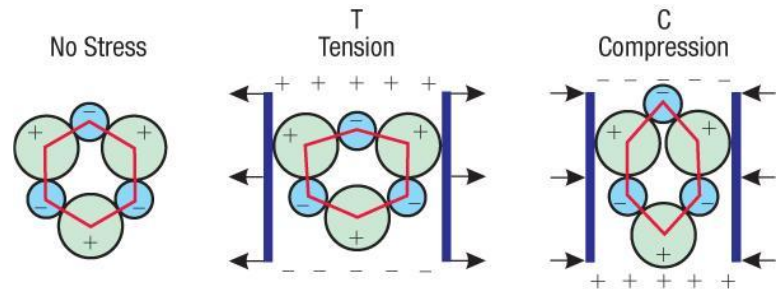


Symmetry loss in 2D systems

Piezoelectricity

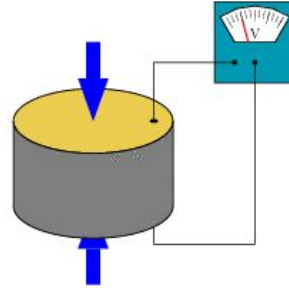
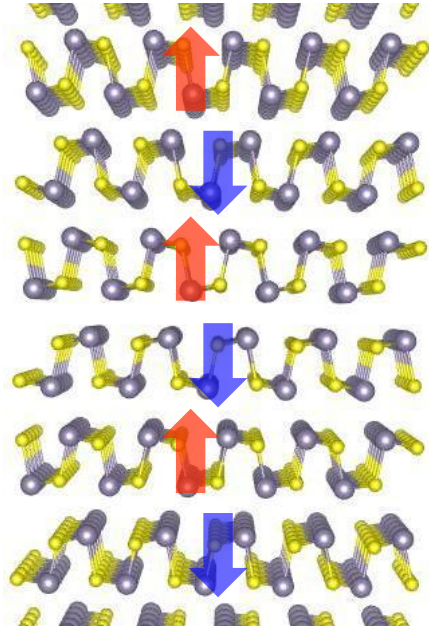


Piezoelectric Effect in Quartz



Symmetry loss in 2D systems

Piezoelectricity



Enhanced piezoelectricity and modified dielectric screening of two-dimensional group-IV monochalcogenides

Lídia C. Gomes, A. Carvalho, and A. H. Castro Neto

Centre for Advanced 2D Materials and Graphene Research Centre, National University of Singapore, 6 Science Drive 2, 117546, Singapore

(Received 14 September 2015; revised manuscript received 16 November 2015; published 8 December 2015)

We use first-principles calculations to investigate the lattice properties of group-IV monochalcogenides.

$$e_{ij} = -\frac{\partial \sigma_i}{\partial E_j} = \frac{\partial P_i}{\partial \varepsilon_j}$$

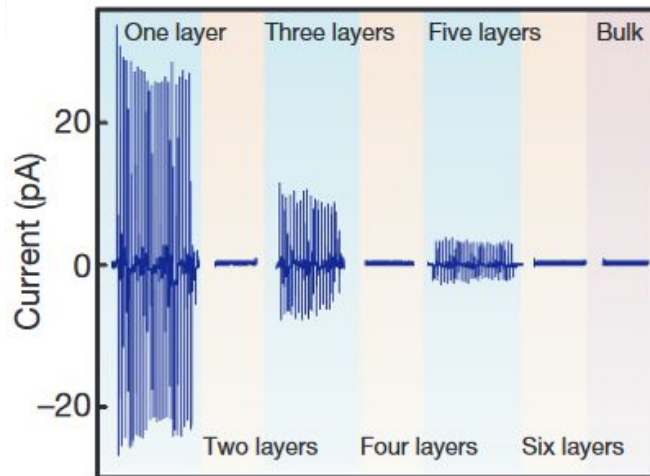
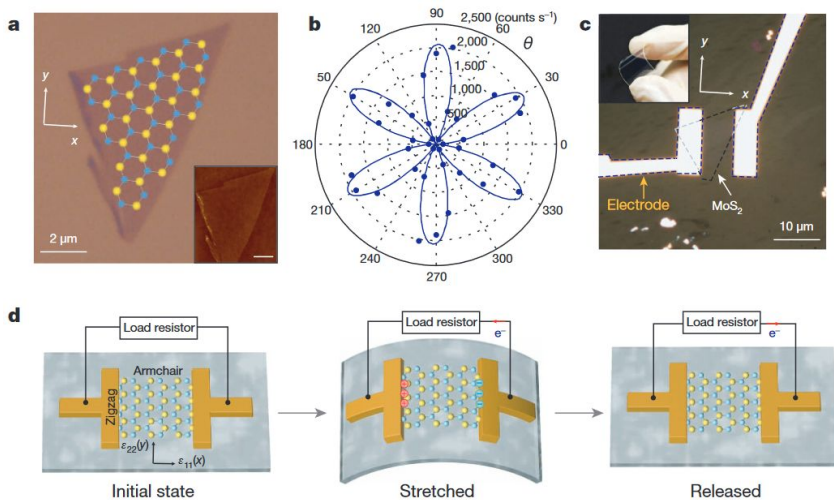
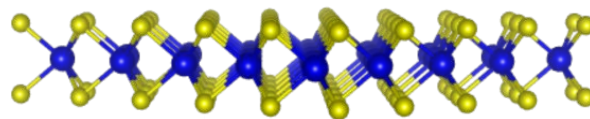
		Clamped-ion			Relaxed-ion		
		e_{32}^{2D}	e_{33}^{2D}	e_{24}^{2D}	e_{32}^{2D}	e_{33}^{2D}	e_{24}^{2D}
SnS	GGA-PBE	-4.73	0.29	-4.39	0.76	23.36	15.70
	vdW-TS	-5.01	0.47	-4.75	2.27	18.94	15.54
SnSe	GGA-PBE	-4.89	0.53	-4.67	4.42	24.18	28.17
	vdW-TS	-4.67	0.58	-4.29	6.73	30.25	30.82
GeS	GGA-PBE	-6.69	-1.25	-7.10	-4.97	7.28	0.37
	vdW-TS	-6.89	-0.81	-7.08	-4.64	8.83	2.05
GeSe	GGA-PBE	-7.16	-0.26	-7.37	-3.00	13.26	8.25
	vdW-TS	-7.11	0.35	-7.20	-1.48	16.95	12.48
h-BN		-3.71	3.71		-1.38	1.38	
MoS ₂		-3.06	3.06		-3.64	3.64	
MoTe ₂		-2.98	2.98		-5.43	5.43	

Symmetry loss in 2D systems

Piezoelectricity

Piezoelectricity of single-atomic-layer MoS₂ for energy conversion and piezotronics

Wenzhuo Wu^{1*}, Lei Wang^{2*}, Yilei Li³, Fan Zhang⁴, Long Lin¹, Simiao Niu¹, Daniel Chenet⁴, Xian Zhang⁴, Yufeng Hao⁴, Tony F. Heinz³, James Hone⁴ & Zhong Lin Wang^{1,5}



Muitas (todas?) propriedades interessantes dos materiais 2D surgem devido às fortes correlações eletrônicas.



Modos coletivos!

REVIEWS

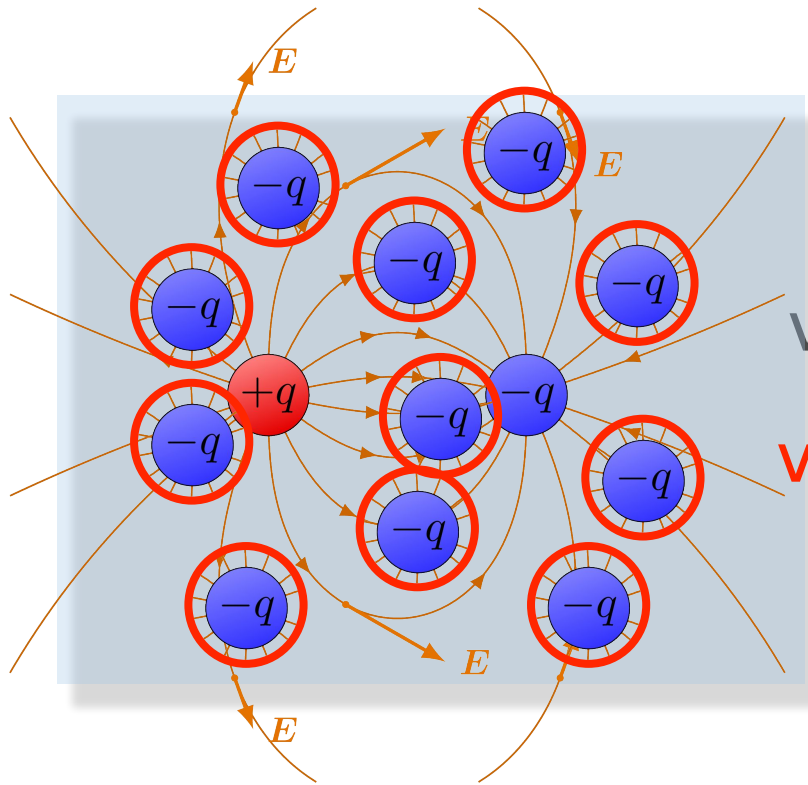


Collective excitations in 2D materials

Aleksandr Rodin^{1,2}, Maxim Trushin¹, Alexandra Carvalho¹ and A. H. Castro Neto^{1,3}

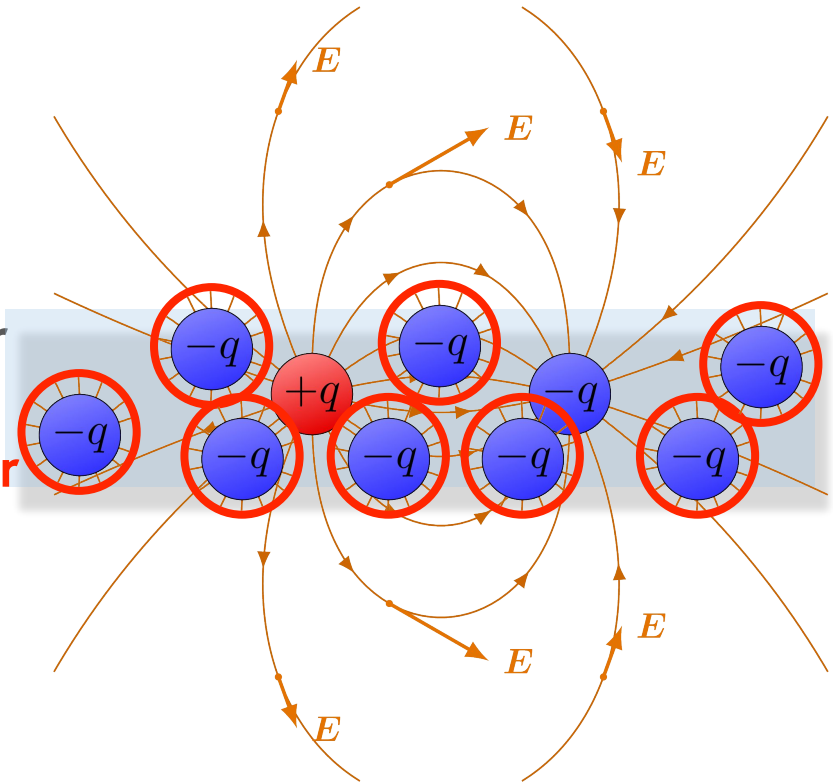
Abstract | Research on 2D materials has been one of the fastest-growing fields in condensed matter and materials science research in the past 10 years. The low dimensionality and strong correlations of 2D systems give rise to electronic and structural properties, in the form of collective excitations, that do not have counterparts in ordinary 3D materials used in modern technology. These 2D materials present extraordinary opportunities for new technologies, such as in flexible electronics. In this Review, we focus on plasmons, excitons, phonons and magnons in 2D materials. We discuss the theoretical formalism of these collective excitations and elucidate how they differ from their 3D counterparts.

New properties due to high electronic correlation
Poor screening in 2D systems

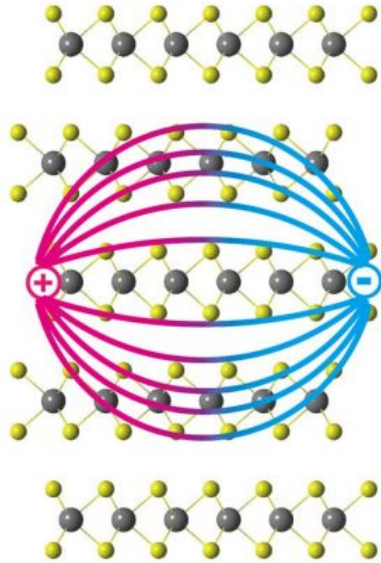


$$V \propto q^2/r$$

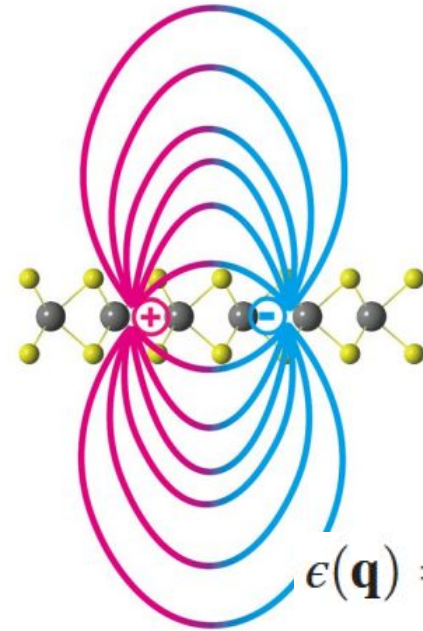
$$V \propto q^2/\epsilon r$$



Modified Coulomb potential in 2D systems



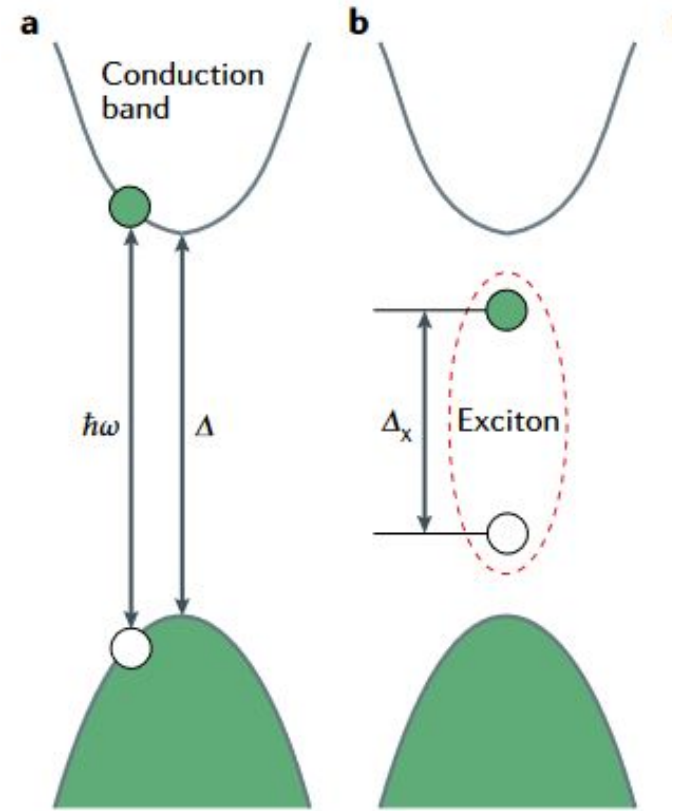
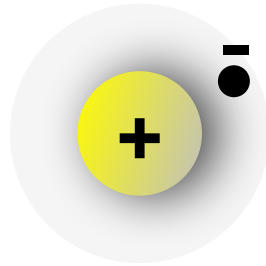
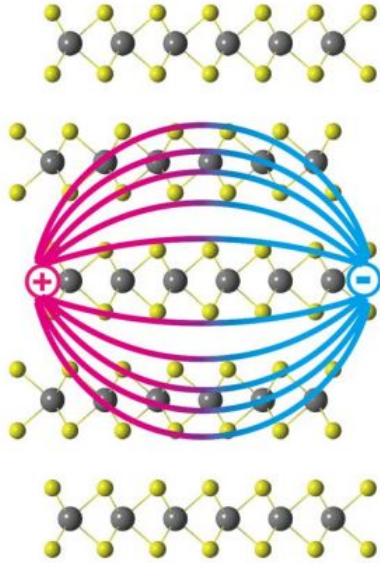
$$V_{3D} = \frac{e}{4\pi\epsilon_r\epsilon_0 r}$$



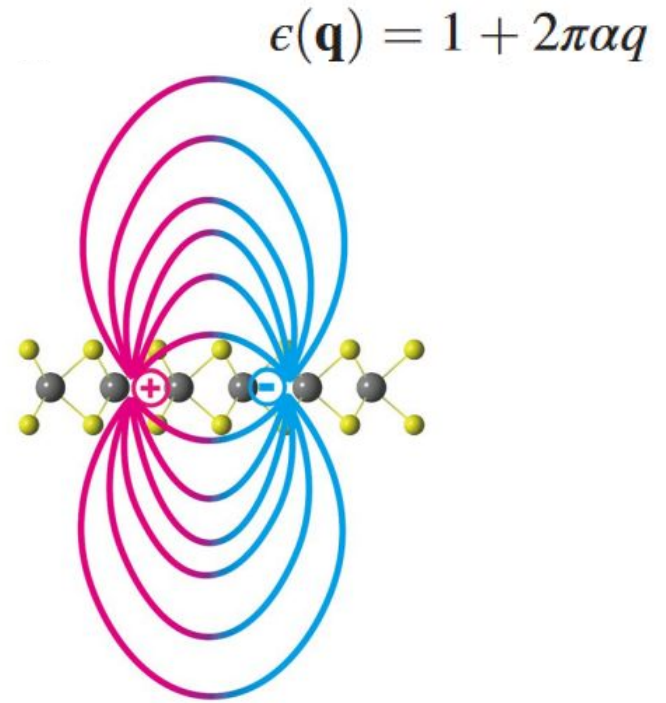
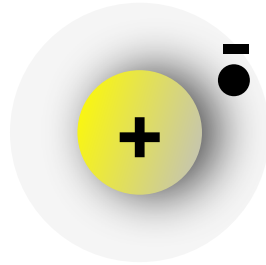
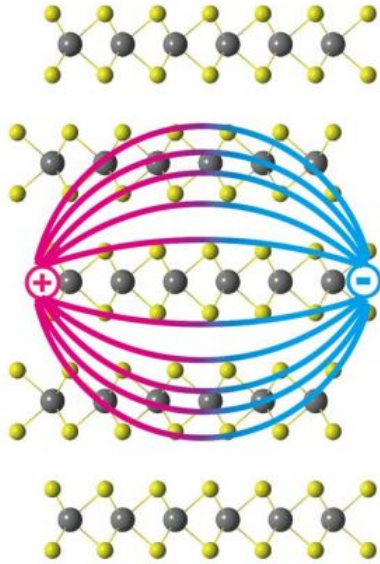
$$\epsilon(\mathbf{q}) = 1 + 2\pi\alpha q$$

$$V_{2D}(r, z = 0) = -\frac{e^2}{8\epsilon_0 r_0} \left[H_0 \left(\frac{\epsilon_r r}{r_0} \right) - Y_0 \left(\frac{\epsilon_r r}{r_0} \right) \right]$$

Excitons



Excitons



Exciton Binding Energy and Nonhydrogenic Rydberg Series in Monolayer WS₂

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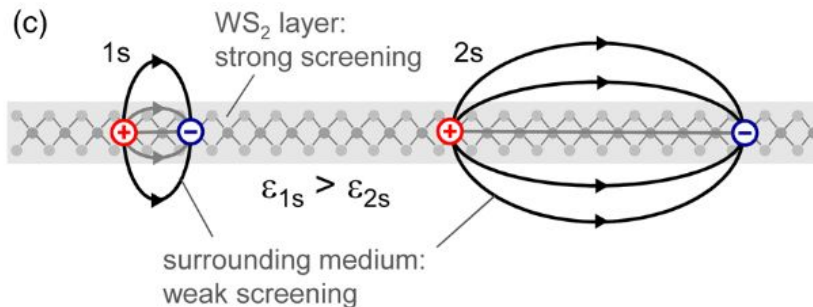
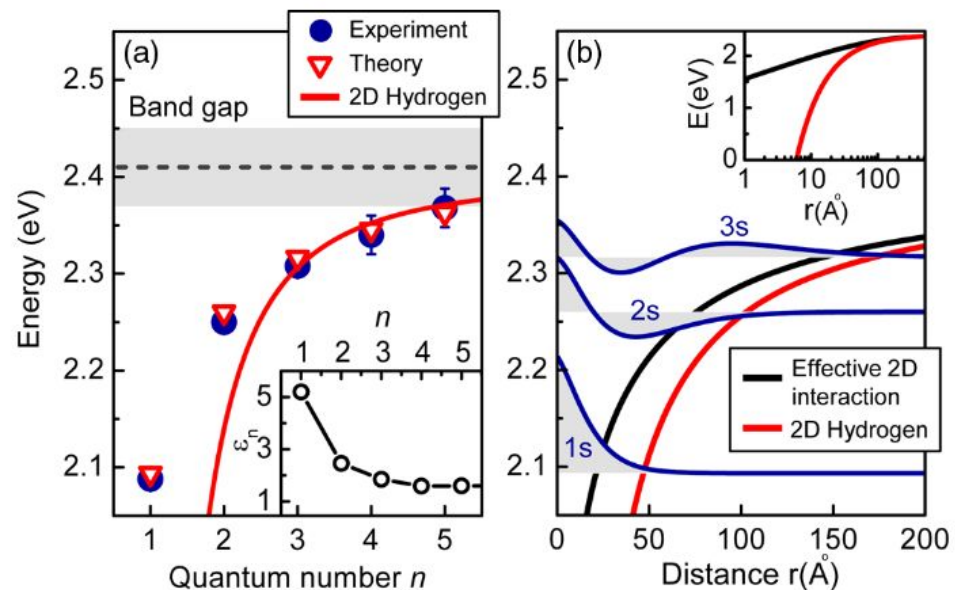
We have experimentally determined the energies of the ground and first four excited excitonic states of the fundamental optical transition in monolayer WS₂, a model system for the growing class of atomically thin two-dimensional semiconductor crystals. From the spectra, we establish a large exciton binding energy

$$V_{eh}(r) = -e^2/\epsilon r$$

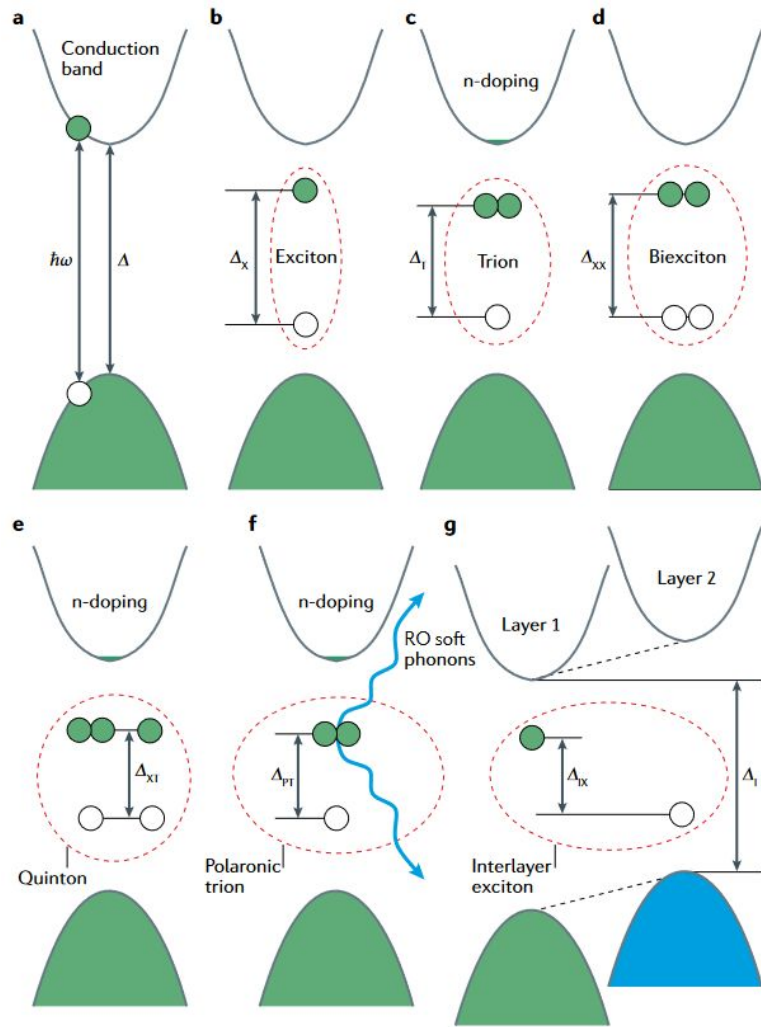
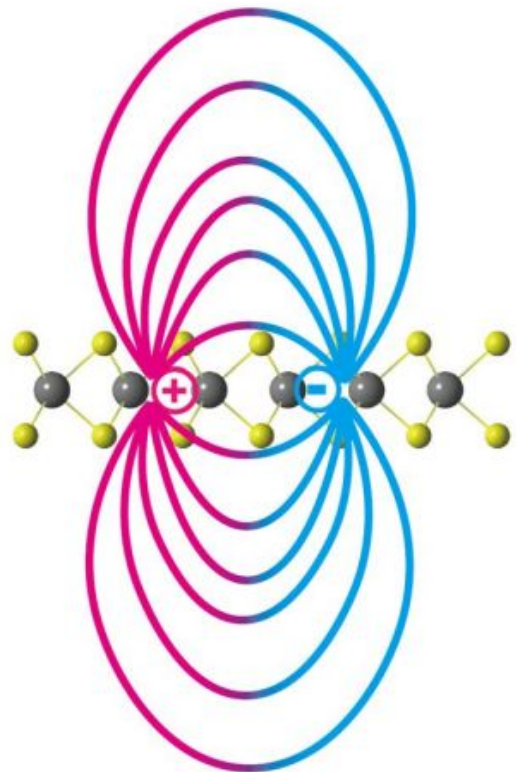
$$E_b^{(n)} = \frac{\mu e^4}{2\hbar^2 \epsilon^2 (n - 1/2)^2}$$

$$\epsilon(\mathbf{q}) = 1 + 2\pi\alpha q$$

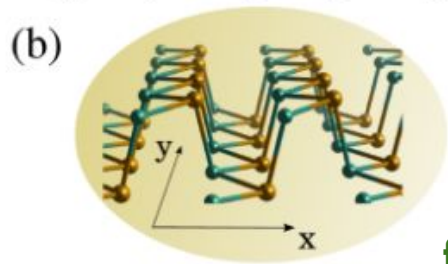
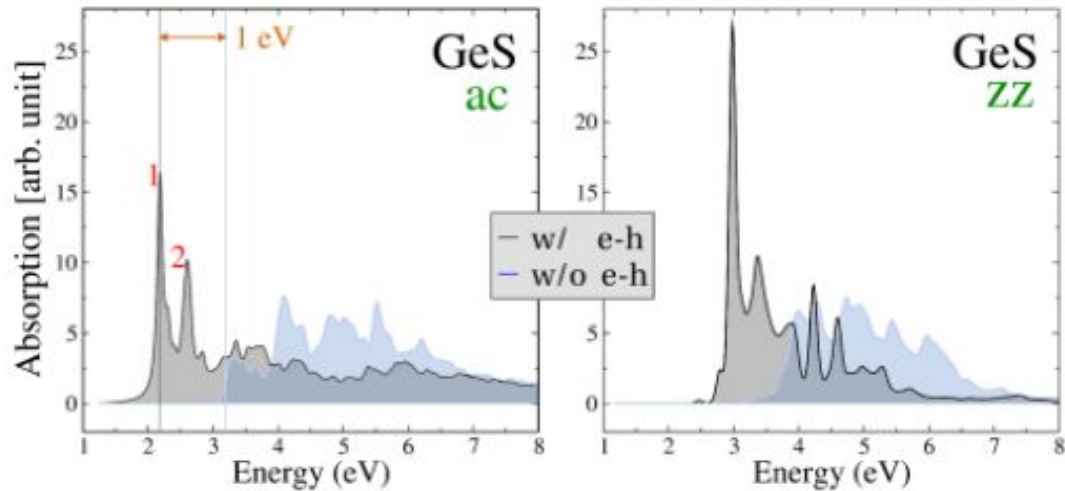
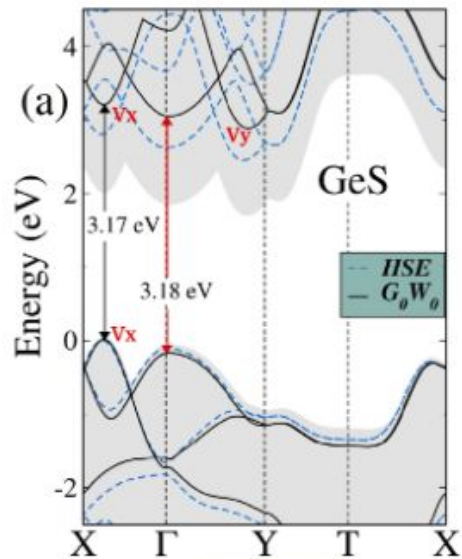
$$V_{eh}(r) = -\frac{\pi e^2}{2r_0} \left[H_0\left(\frac{r}{r_0}\right) - Y_0\left(\frac{r}{r_0}\right) \right]$$



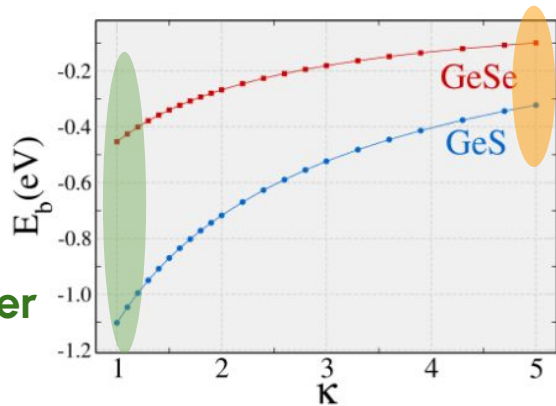
Excitons



Excitons: Group IV-Monochalcogenides



free standing layer



on top of a substrate

Topological excitations: Skyrmions, Merons

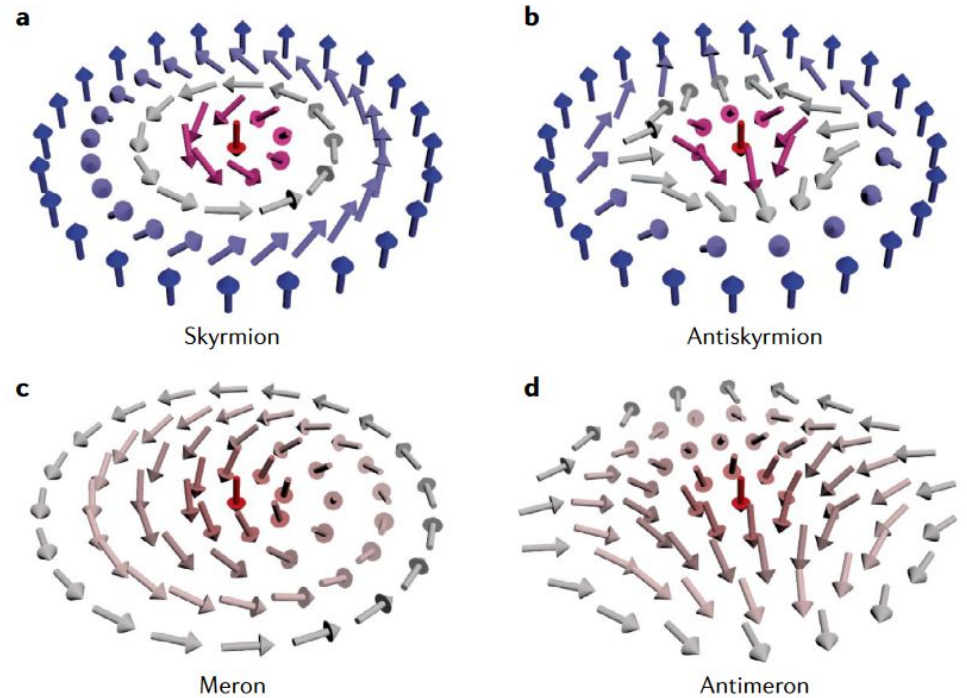


Fig. 7 | **Chiral magnetic spin textures.** a | Skyrmion (spiral-type), topological charge $Q=-1$. b | Antiskyrmions, topological charge $Q=+1$. c | Meron, topological charge $Q=-1/2$. d | Antimeron, topological charge $Q=+1/2$. Reprinted from REF.¹⁴⁸, Springer Nature Limited.